

SIPM for single photon detection (SiPM trends / applications)

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Outline (and disclaimer)

- A little bit of history and SiPM basics
- SiPM DCR
- Some SiPM applications in HEP/NP (calorimeters as example, with intermezzo on radiation damage)
- SiPM for PID: Single-photon sensitivity and RICH detectors and ToF
- Potential impact of new technologies

“emphasis on sensors, not on detectors”

DISCLAIMER: not at all time to develop here a full-swing review. Tried to mix some pedagogical intro plus highlights from *some* detectors (reflecting my background) with lesson learned + *some* recent R&D for detectors under construction + progress in the technology.

LINK effort: many slides with many links. Not good for a supercommunicative talk, but hope it is useful for further studies



*Take
home message



SiPMs turning 25.... (or 30...)



Nuclear Physics B (Proc. Suppl.) 61B (1998) 347–352

PROCEEDINGS
SUPPLEMENTS

Limited Geiger-mode silicon photodiode with very high gain

G. Bondarenko^a, B. Dolgoshein^a, V. Golovin^b, A. Ilyin^a, R. Klanner^c, E. Popova^a

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^bCentre of Perspective Technology and Apparatus (CPTA), Moscow, Russia

^cDESY, Hamburg, Germany



B. Dolgoshein

The novel type of the Silicon Photodiode – Limited Geiger-mode Photodiode (LGP) has been produced and studied. The device consists of many $\approx 10^4$ mm^{-2} independent cells ≈ 10 μm size around n^+ -"pins" located between p-substrate and thin SiC layer. Very high gain more than 10^4 for 0.67 μm wave length light source and up to $6 \cdot 10^5$ for single electron have been achieved. The LGP photon detection efficiency at the level of one percent has been measured.

1. INTRODUCTION

The high gain ($> 10^4$) silicon detectors may have important applications in high energy and nuclear physics as:

-compact insensitive to the B-field fast photodetectors for electromagnetic calorimeters and preshower detectors.

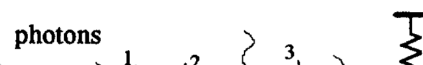
-small size ($\approx 0.1 \text{ mm}^2$) single photon detectors for scintillator fibre trackers.

-very fast (≤ 100 ps) pixel particle detectors for time of flight measurements.

In this paper the different modifications of such a photodiodes and their mode of the operation have been presented.

2. THE STRUCTURE OF PHOTODIODE

The schematic photodiode structure (basic version) is shown in Fig.1. It consists of pin like



Around 1990 the initial prototypes of SiPM (**MRS** Metal- Resistor Semiconductor APD's) were invented in Russia (*V. Golovin, Z. Sadygov, N. Yusipov (Russian patent#1702831, from 10/11/1989)*)

Pioneering work in Moscow, MEPHI/CPTA as well as at JINR/Dubna described in:

- Saveliev, NIMA 442 (2000) 223
- Golovin, NIMA 539 (2005)
- Dolgoshein, NIMA 563 (2006)

And references therein

According to this [nice talk by E. Popova](#) (MEPHI) at 2019 Rindberg School SiPMs are turning 30 exactly this year

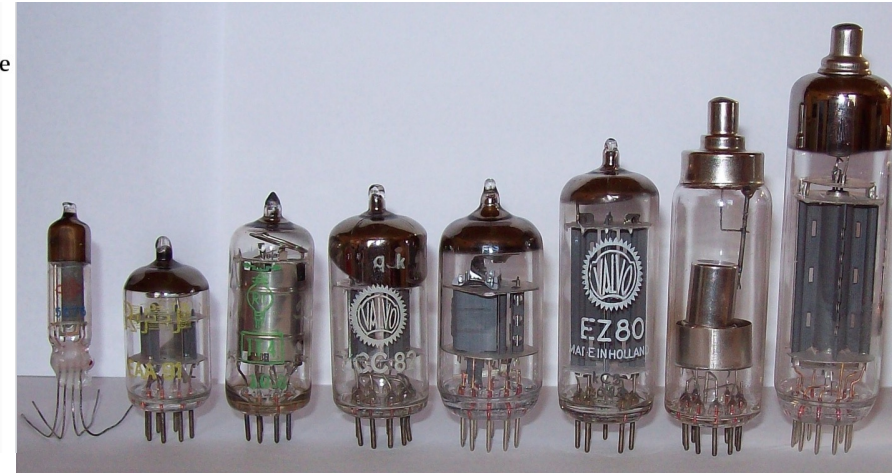
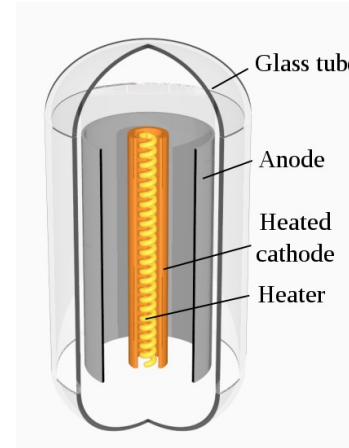
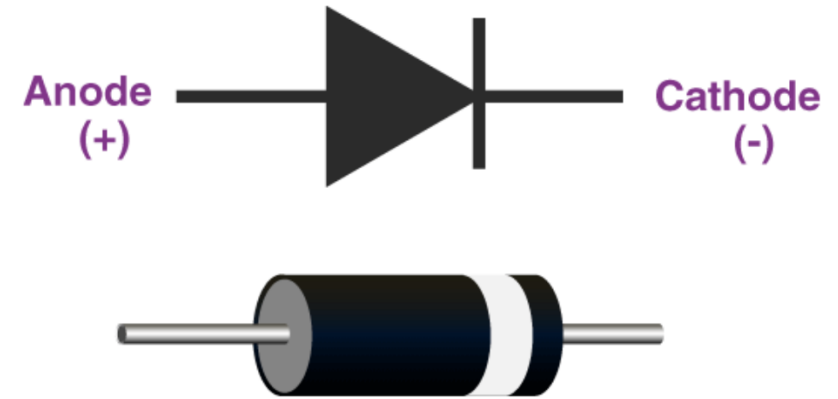
What is a SiPM? (in few – historical - steps) (I)

Remember first what is a **diode**:

A diode is a two-terminal electronic component that conducts electricity primarily in one direction. It has high resistance on one end ($\rightarrow \infty$) and low resistance ($\rightarrow 0$) on the other end.

We speak therefore about asymmetric conductance of the diodes.

First engineered as thermionic valve (or thermionic tube) (Fleming, 1904): it uses electrons emitted from a hot cathode. Electrons can flow in only one direction!



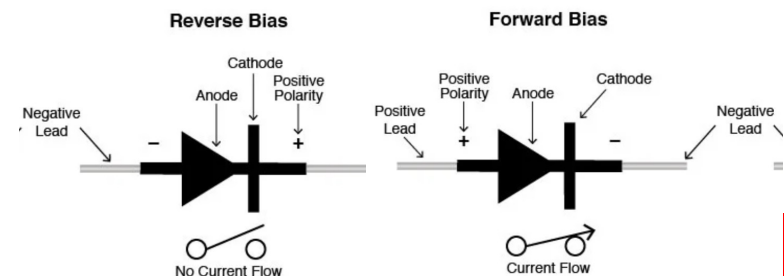
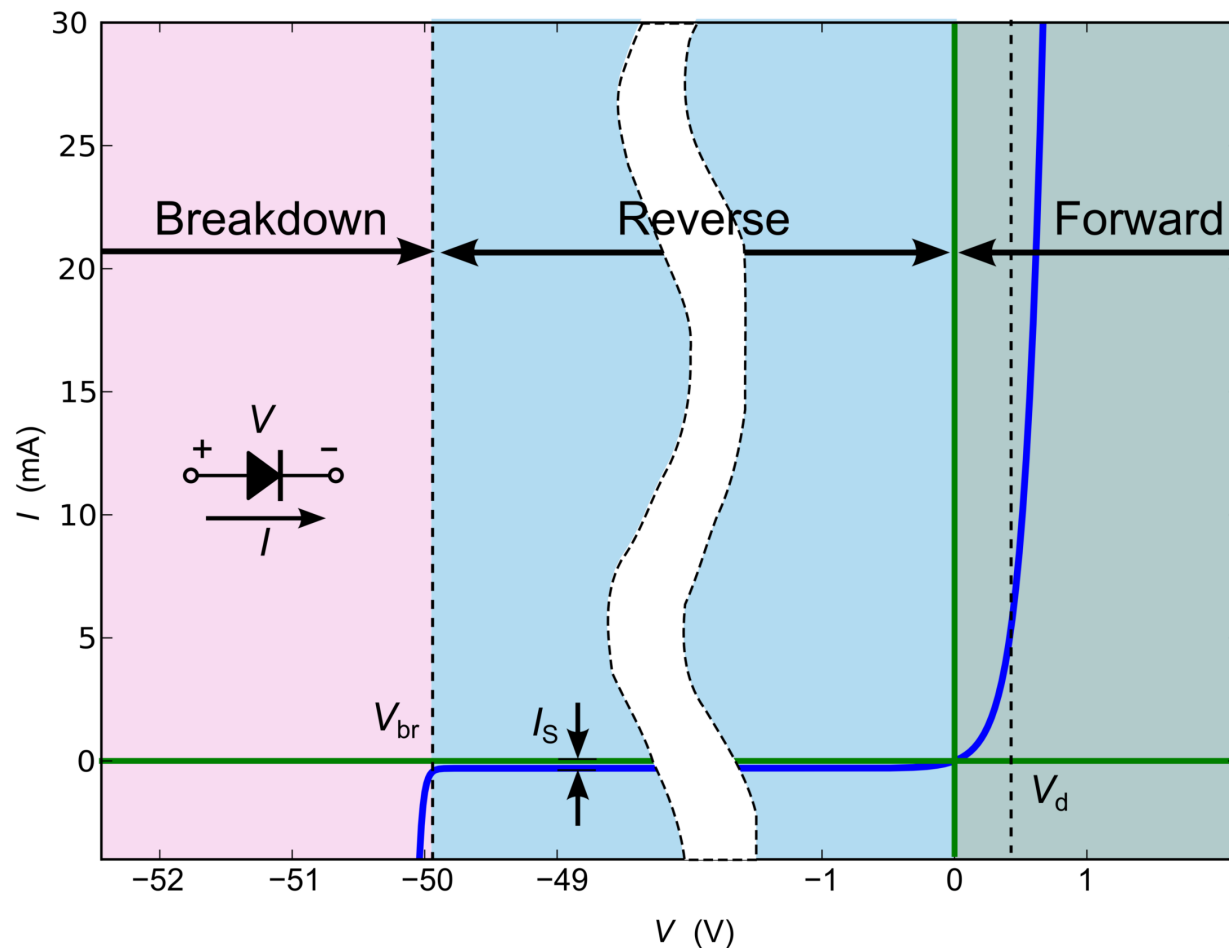
What is a SiPM? (in few – historical - steps) (II)

Remember about **semiconductor diode**:

Made by a p-n junction connected to two electrical terminals.
(discovery of asymmetric electric conductance across crystalline mineral and a metal dates back to 1874)

Nowadays semiconductor diodes technology largely based on silicon. Impurities on the silicon are added to create regions with negative charge carriers (electrons) → n-region or positive (holes) → p-region. The depleted region acts as an insulator and its width is regulated by the **built-in potential** (it stops recombination)

- Without voltage applied: momentary flow from n to p-side --> “depletion region”
- With voltage applied (higher to p-side) → electrons can flow through the depletion region (not viceversa) → a diode!



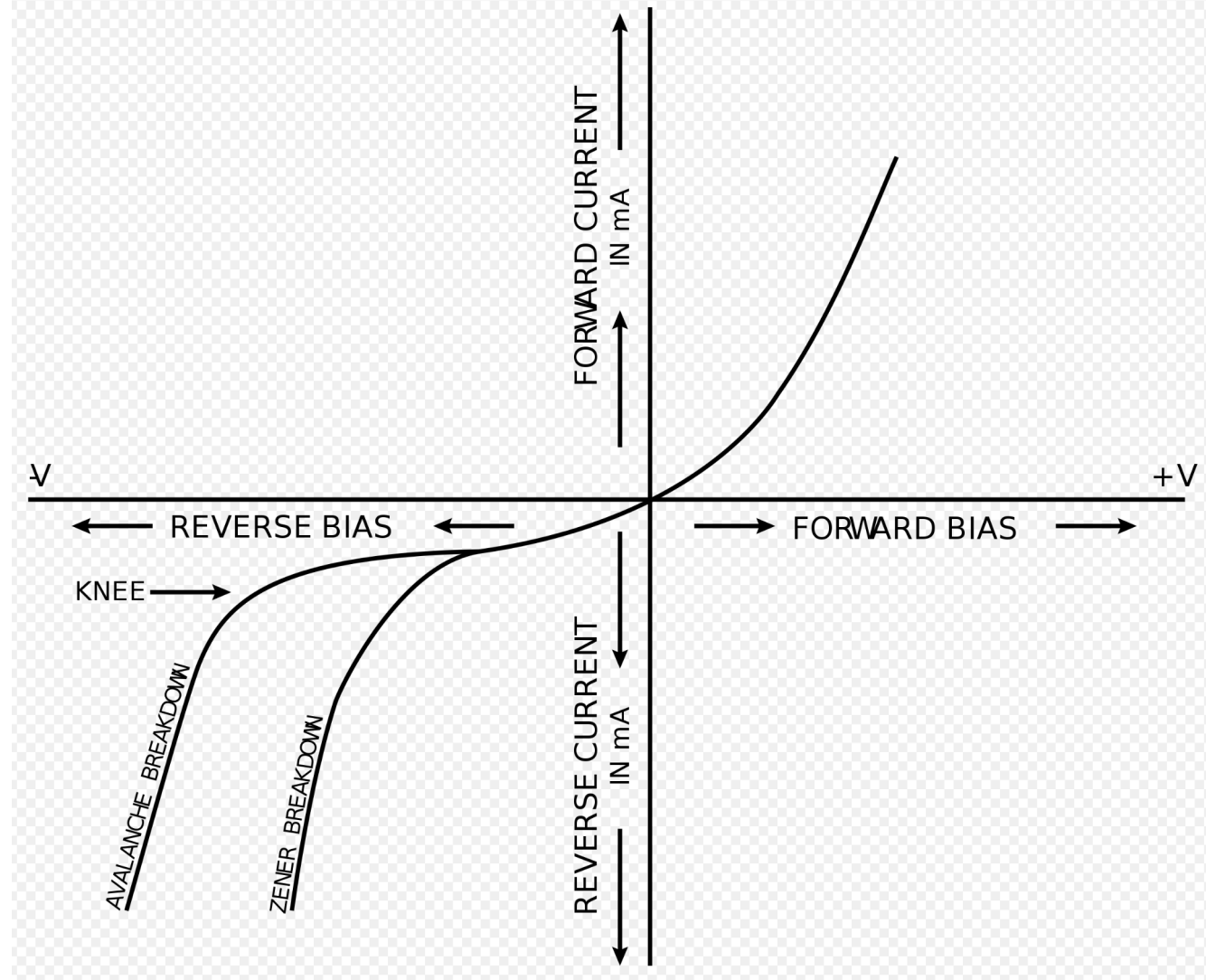
What is a SiPM? (in few – historical - steps) (III)

What is an avalanche diode?

At large reverse polarity something different happens!
This happens beyond PIV (Peak Inverse Voltage).

Essentially mobile electrons at sufficiently high V before reaching n-region can free other bound electrons... and this creates in turn a high flow of current (“avalanche”)

The diode is no longer an insulator.
 V “breakdown” concept”

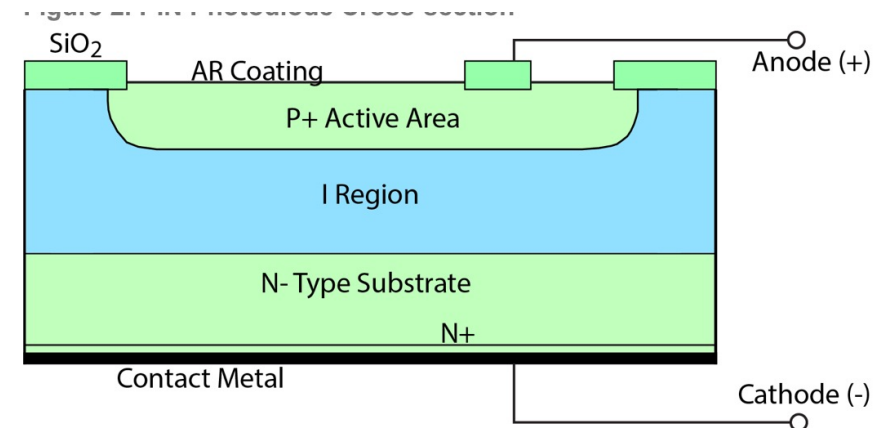
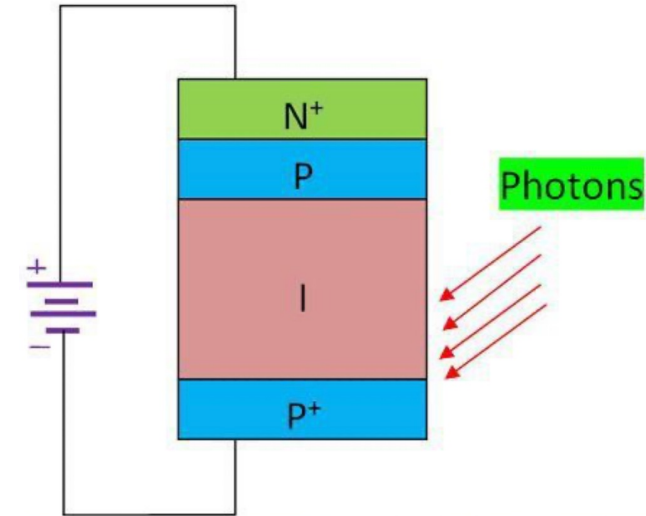
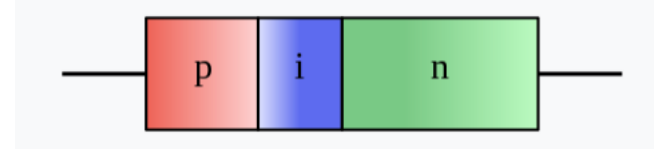


What is a SiPM? (in few – historical - steps) (IV)

What is instead a **photo diode**?

photodiode is based on a **PIN junction**

- The intrinsic region increases the depleted region with respect to pn junction: larger and constant-size
- This increases the region where an incident photon can generate an electron-hole pair → photodiode
- Note photodiodes are operated in reverse voltage: the voltage sweeps charges out of depleted region → current

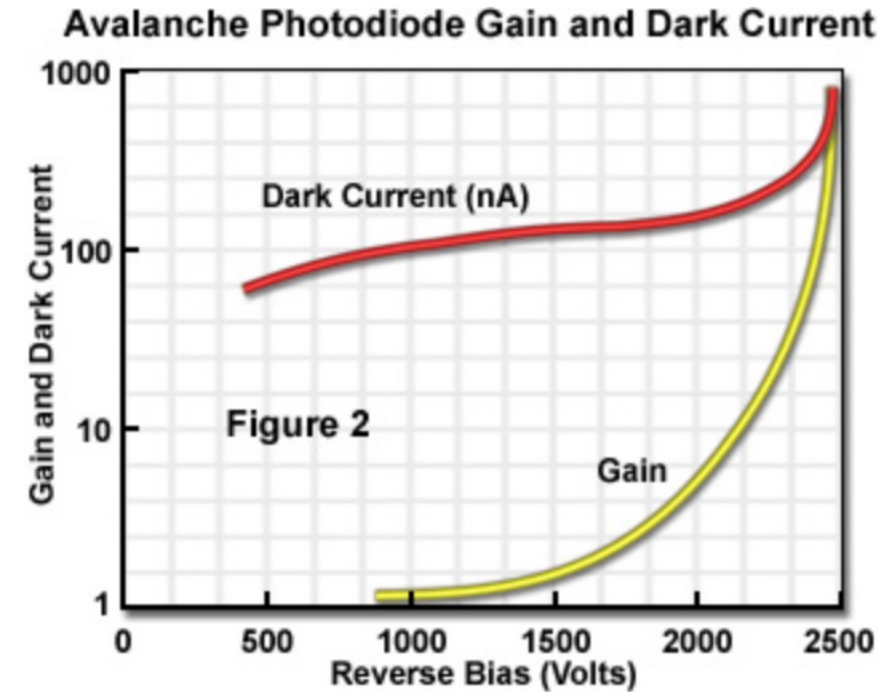
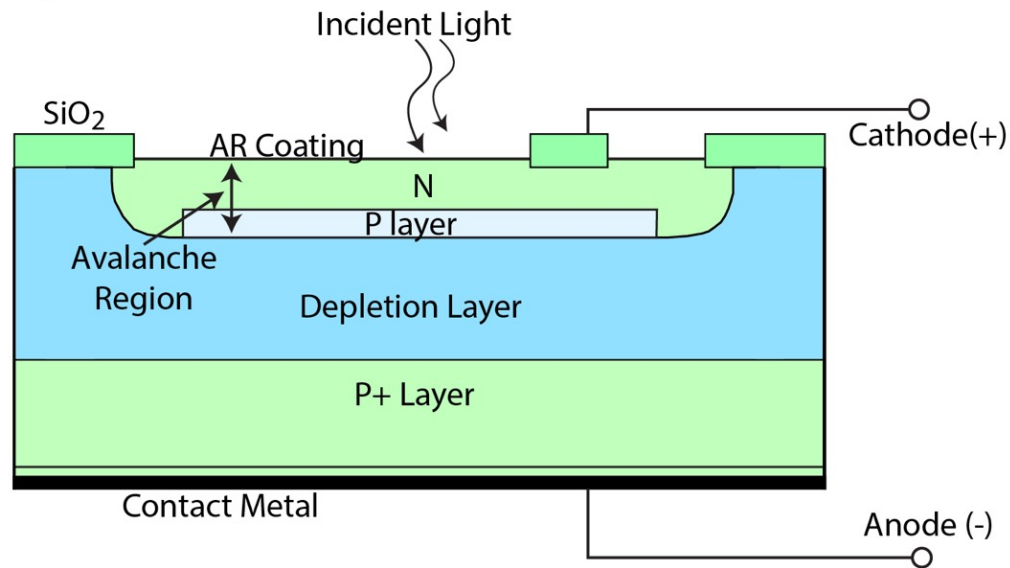


Jun-ichi Nishizawa invented both photodiode (1950) and **avalanche photodiode** (1952)

What is a SiPM? (in few – historical - steps) (V)

Let's move to an **avalanche photodiode**

If you apply high reverse bias and the field is high enough carriers (electrons in particular) can generate (“impact ionization”) other charges in the depletion region: current will flow! → avalanche



Similar to PIN but depletion region relatively thin

Concept of avalanche similar to what we do in traditional PMT via dynodes

What is a SiPM? (in few – historical - steps) (VI)

Penultimate step toward SiPM is the **SPAD concept: Single-photon avalanche photodiode**

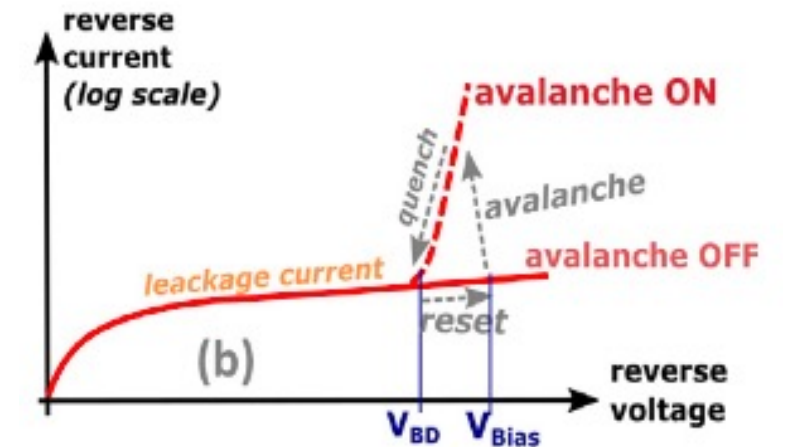
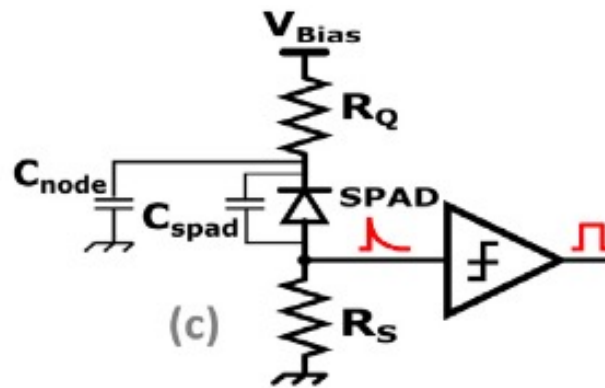
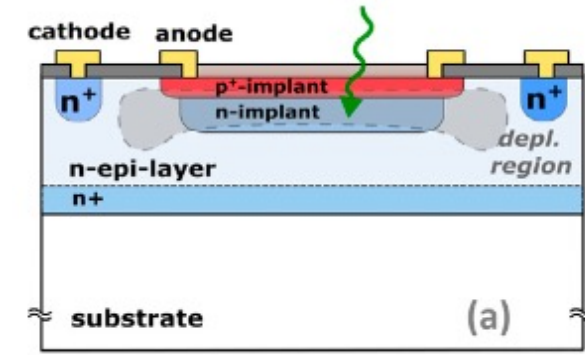
SPAD:

- APD designed working **beyond breakdown voltage**
- **Electrical field can reach few 10^5 V/cm**
- Avalanche multiplication as internal gain mechanism, but a single carrier injected can trigger self-sustained avalanche
 - Geiger-mode (Gm-APD)
- Single photon sensitivity
- Need of a “quenching circuit”

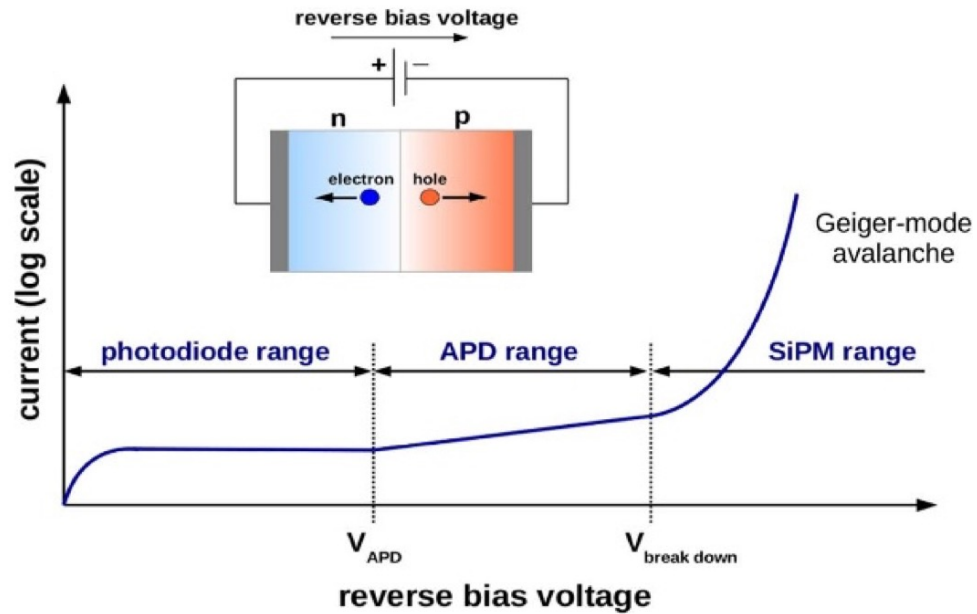
With current increases R_q creates a voltage drop such the V_{bias} goes below breakdown and avalanche stops.

$$\tau_{reset} = R_q \cdot (C_{SPAD} + C_{node})$$

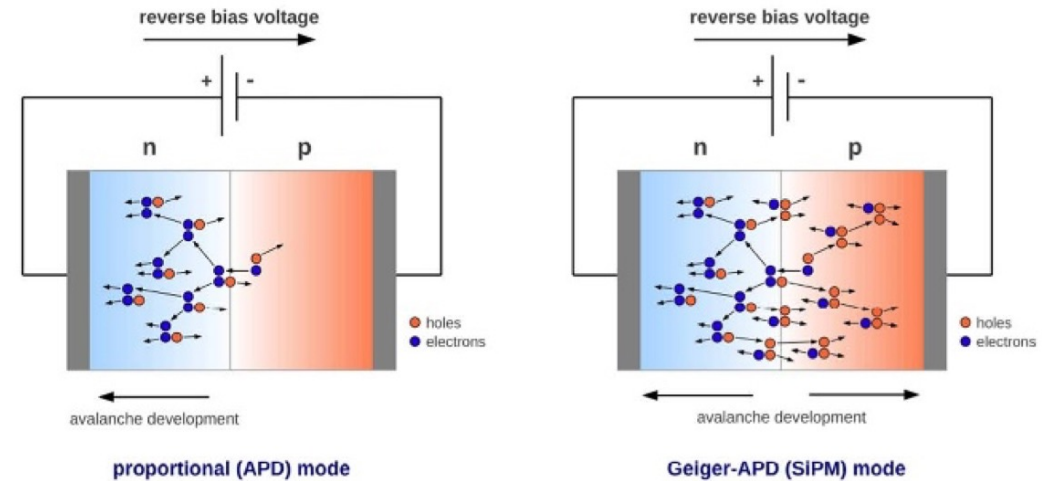
Figures from F. Acerbi and S. Gundacker, NIM A 926 (2019) 16-35



In SPAD, avalanche is self-sustained



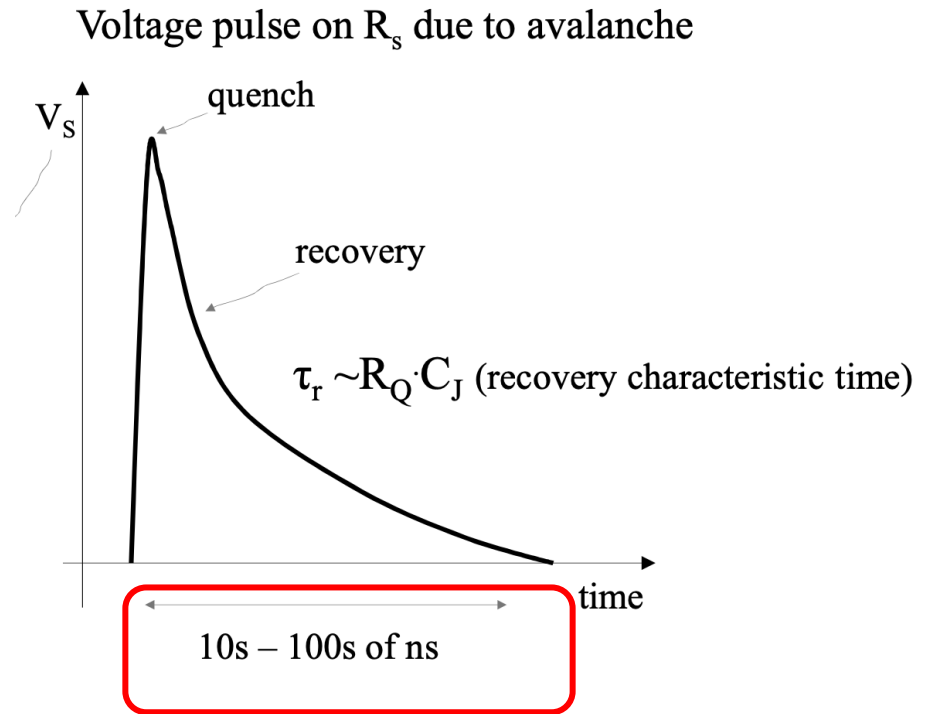
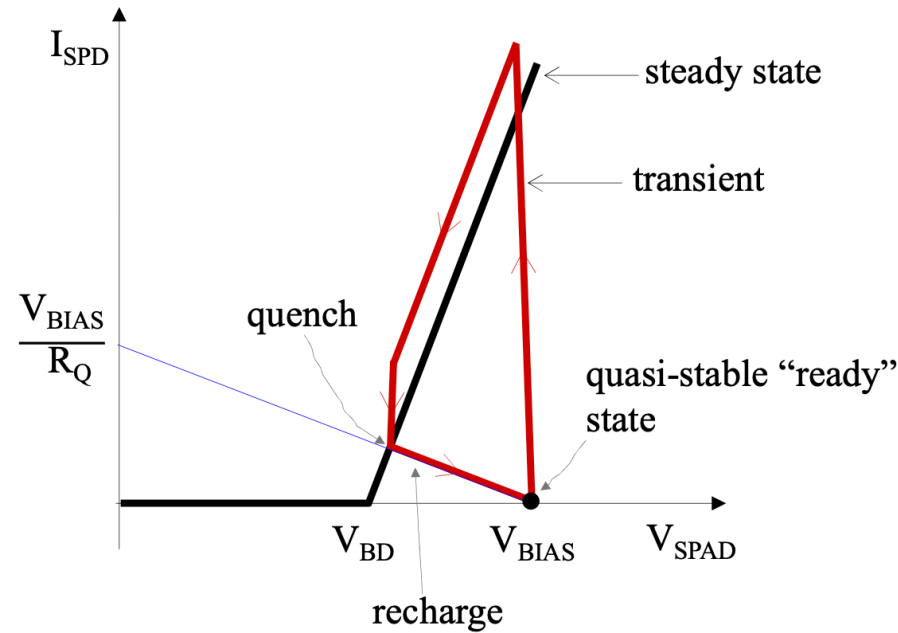
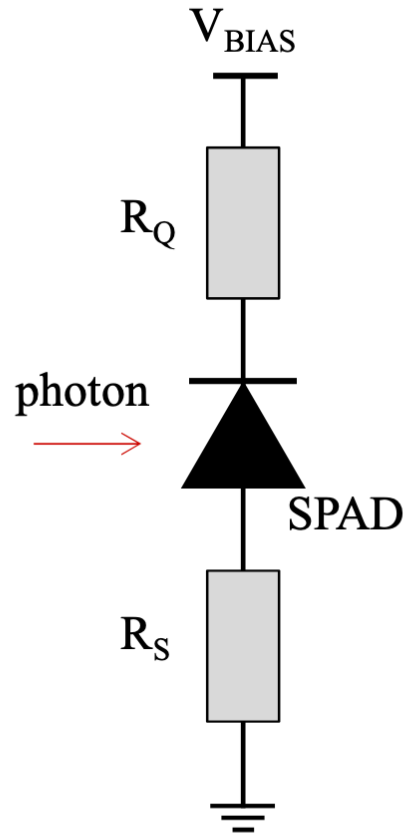
(a)



(b)

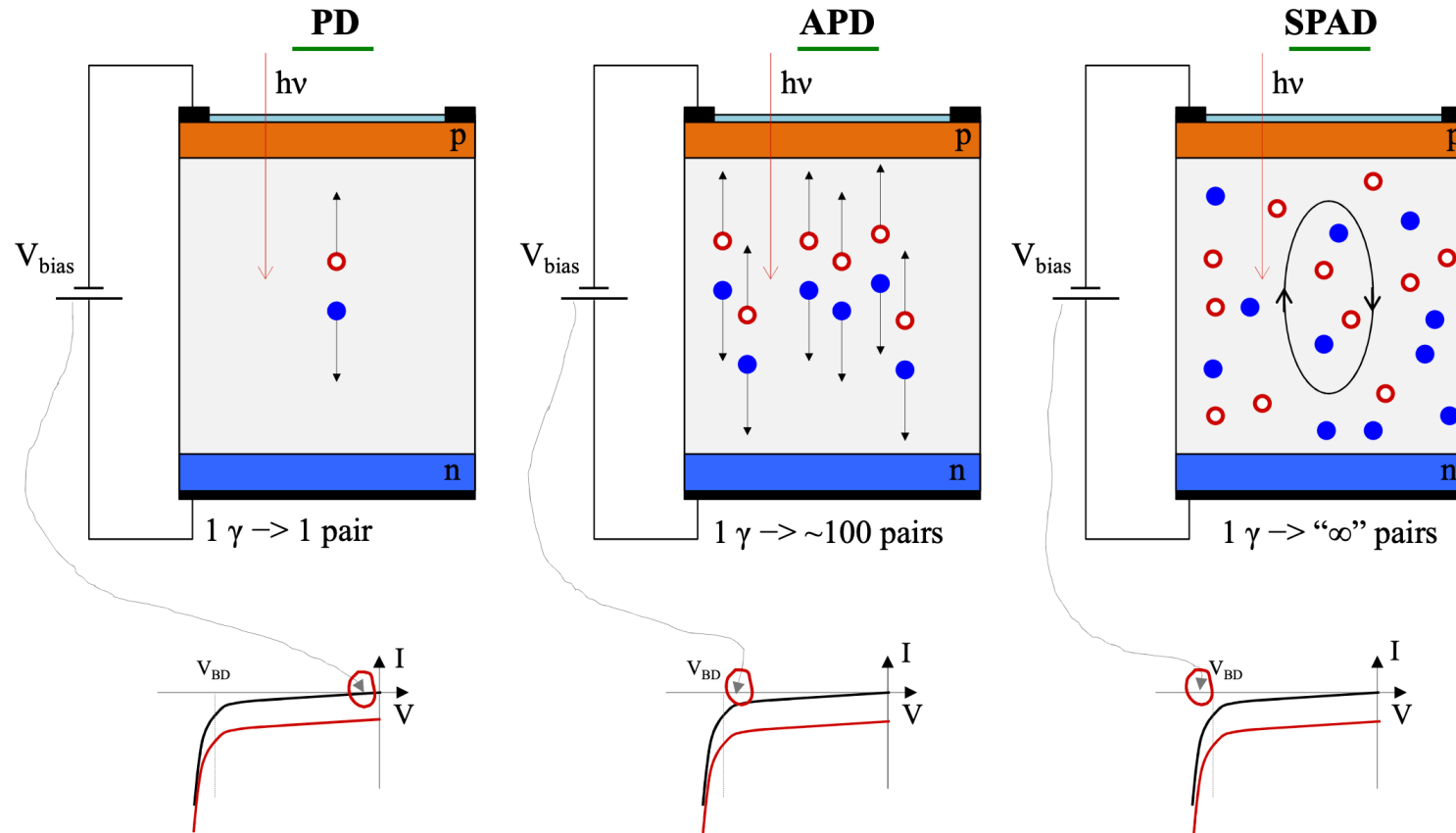
In the APD only electrons can sustain the avalanche, whereas in a SPAD holes will perform impact ionization as well.

SPAD: further details on quenching and signals



A first summary after 12 slides

PD, APD, and SPAD



1/17/2019

SiPM and SPAD

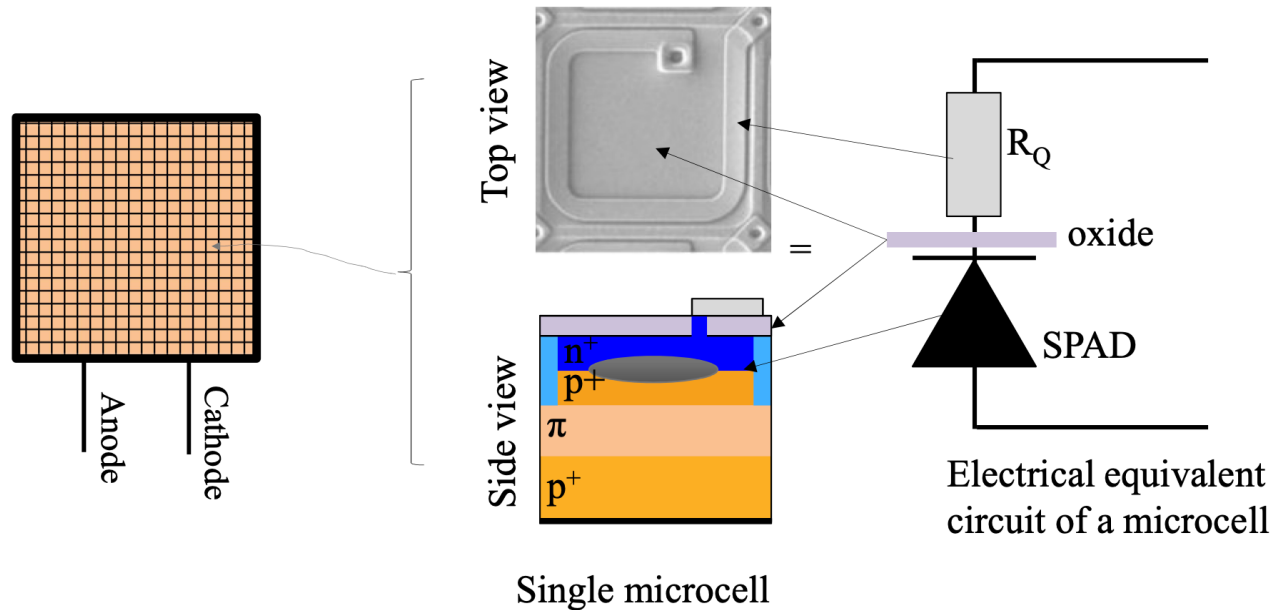
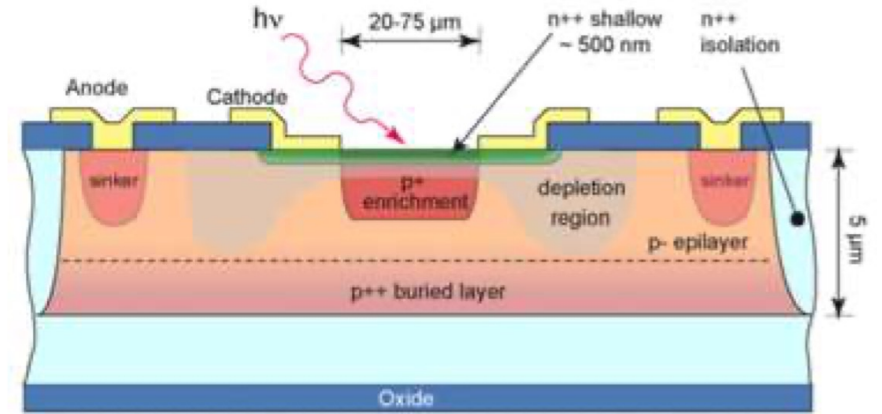
Slide # 7

(courtesy: S.S. Piatek, "SiPM and SPAD: Emerging Applications for Single-Photon Detection")

What is a SiPM? (in few – historical - steps) (VII)

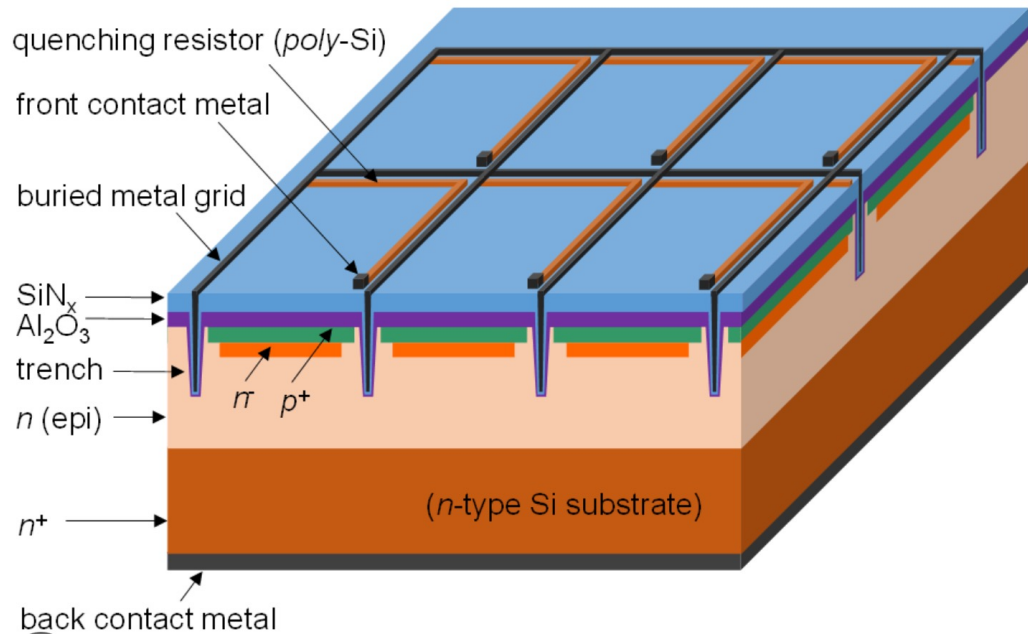
Last step toward SiPM is the **SPAD array concept**:
How can we pack many SPAD in a suitable sensor?

Structure of microcell replicated in an array!



Side note:
SiPM is not an imaging device: all microcells share common current summing all cells!

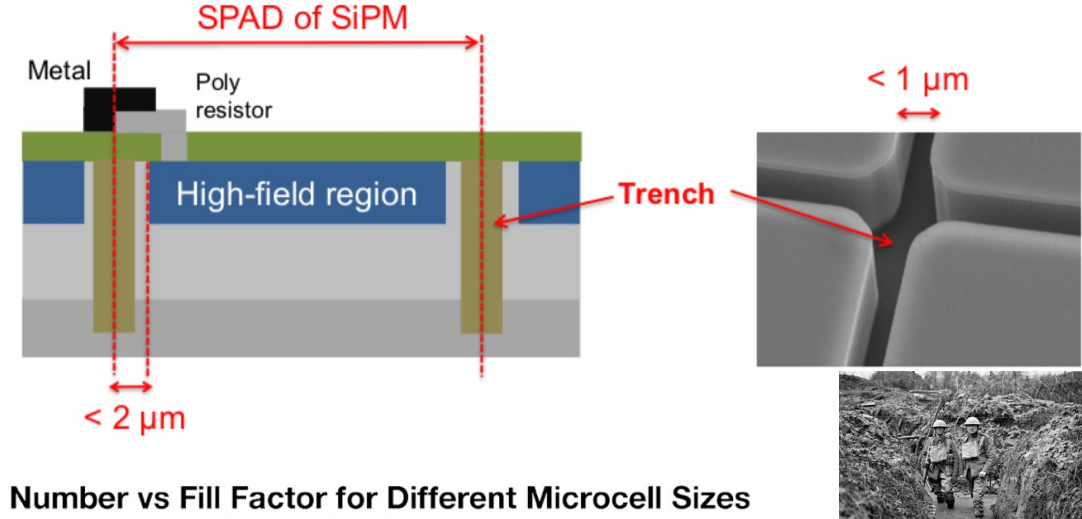
SiPM: microcells, arrays and trenches



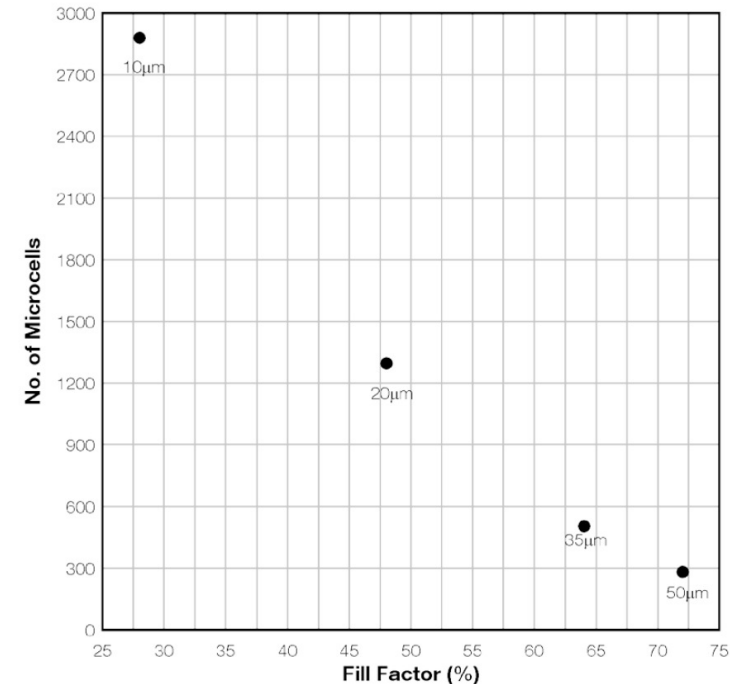
- Typical micro-cells size is between 15-75 μm
- Typical SiPM array size is 3x3 mm² o 1x1 mm²
- Using 3x3 mm² → typically 200x200-40x40 SPAD

We have a tradeoff between **microcell size** and **fill factor**

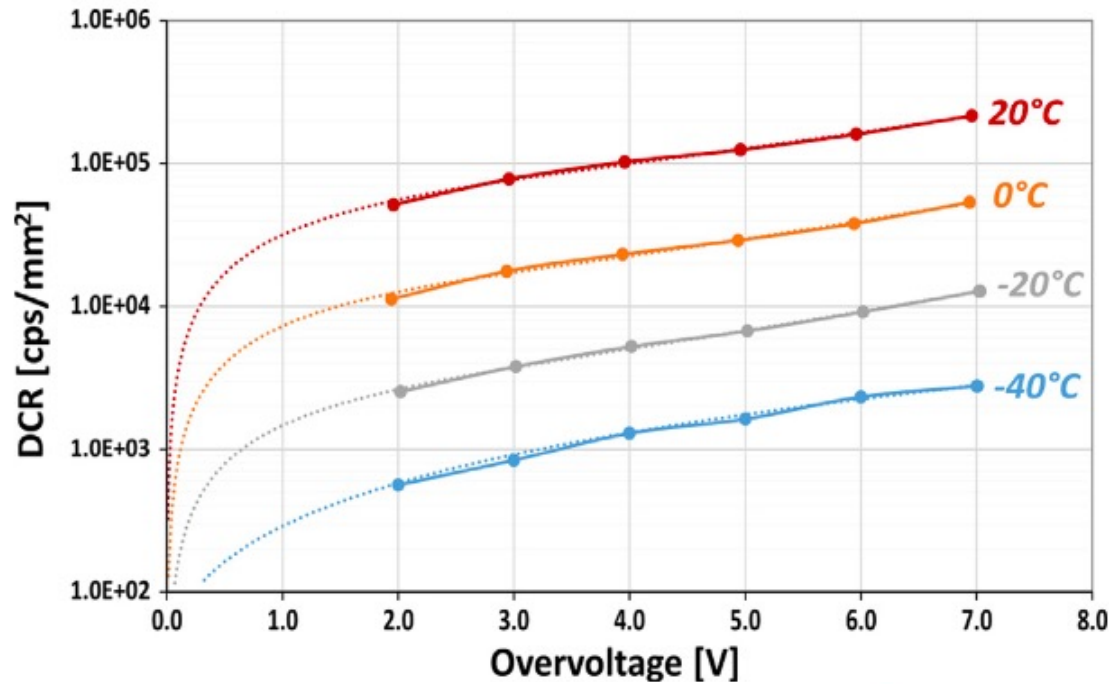
Poly-Si → polycrystalline silicon → high R



Microcell Number vs Fill Factor for Different Microcell Sizes
 MicroFC-100XX-SMT



SiPM DCR ("Dark Count Rate")

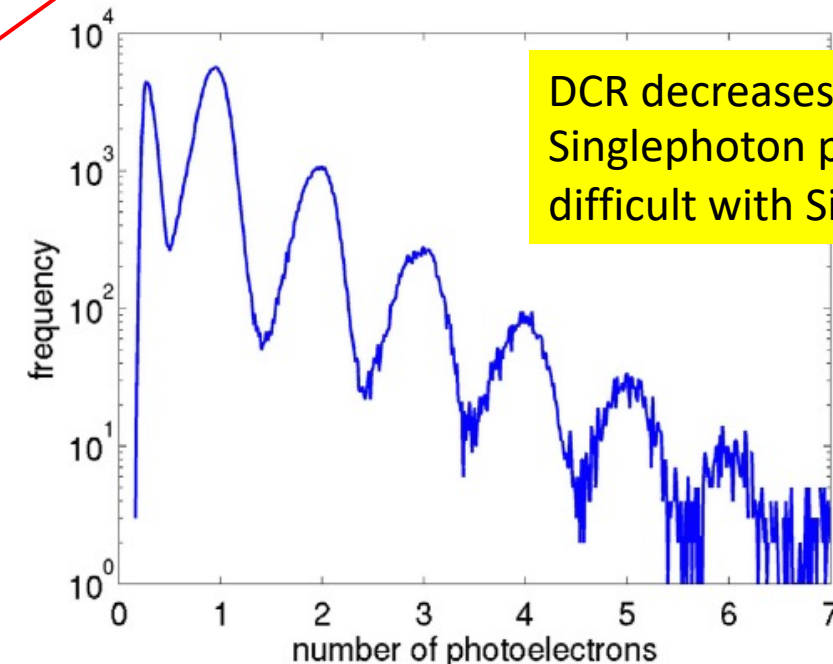
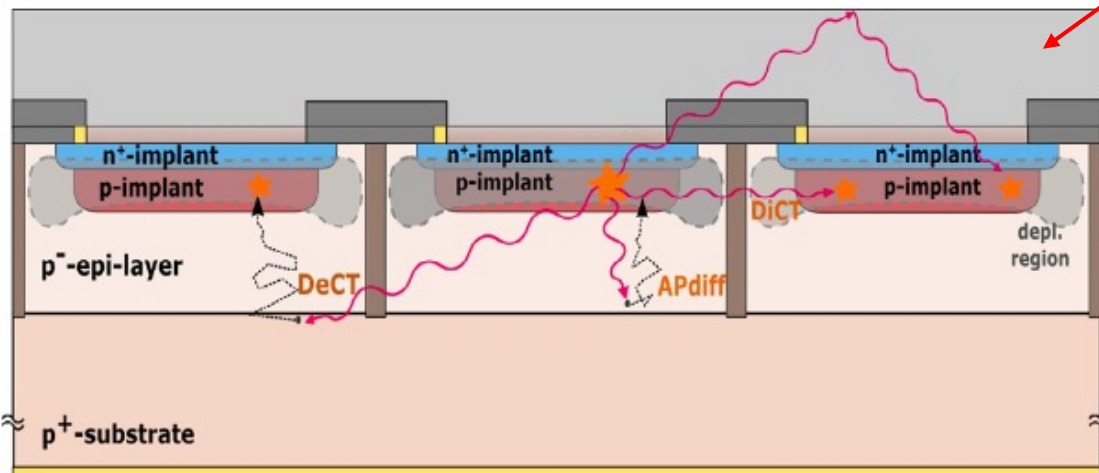


Reduction of DCR by a factor 2-2.5 every 10 degrees

Primary noise: avalanche triggered by thermally generated carriers or tunnelling in high-field region (depends on thickness/purity of depleted layer)

Correlated noise: (after a primary event):

- Afterpulsing (same cell): due to carriers trapped in the depleted region and then released
- **Optically induced cross-talk** (in same or close SPAD)



SiPM optimization for cryo detectors (I)

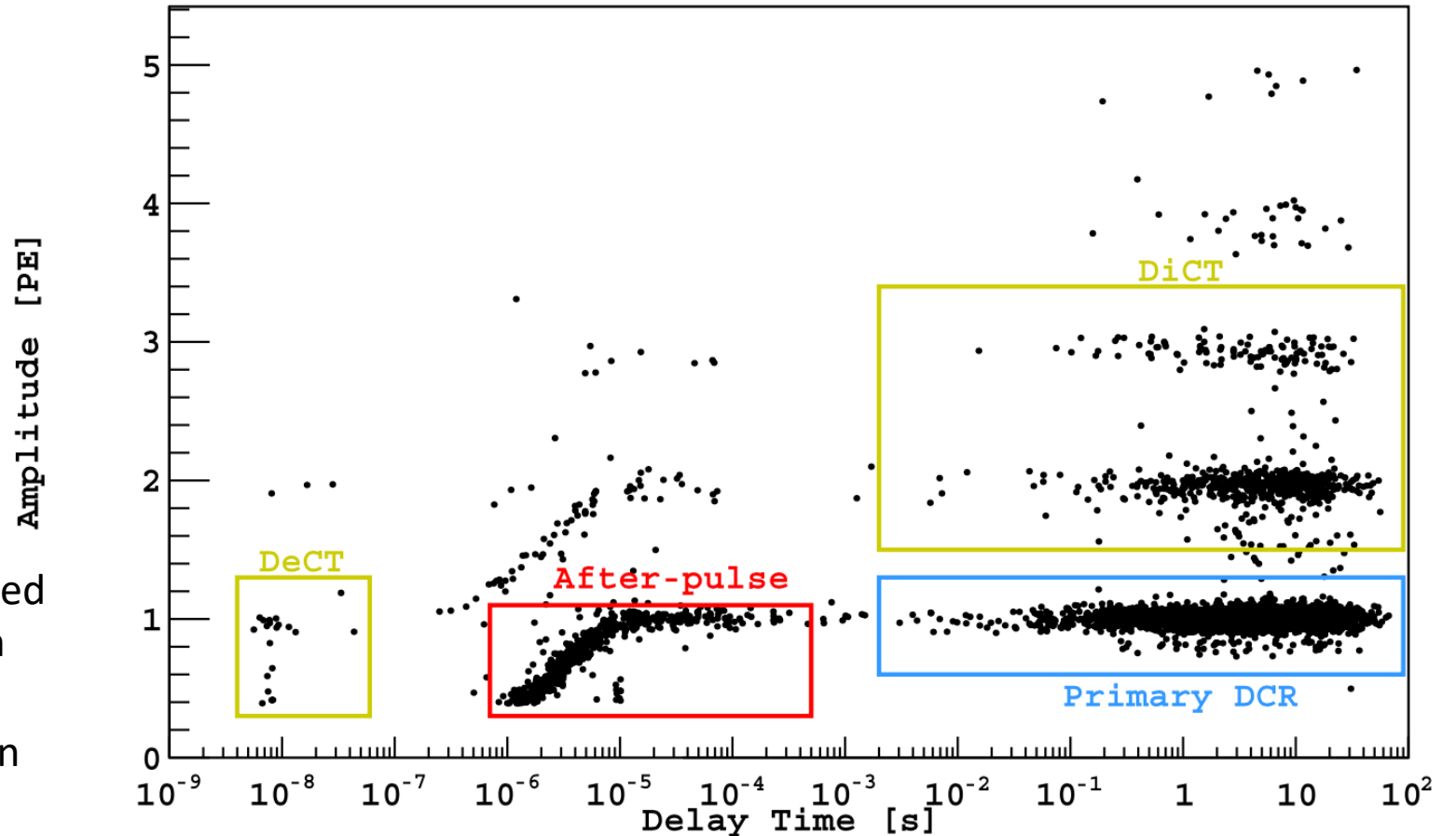
- characterization studies for Darkside
- 25x25 μm SPAD
- no light stimulation
- 77 K

F. Acerbi et al, IEEE Trans. 64 (2017) 521

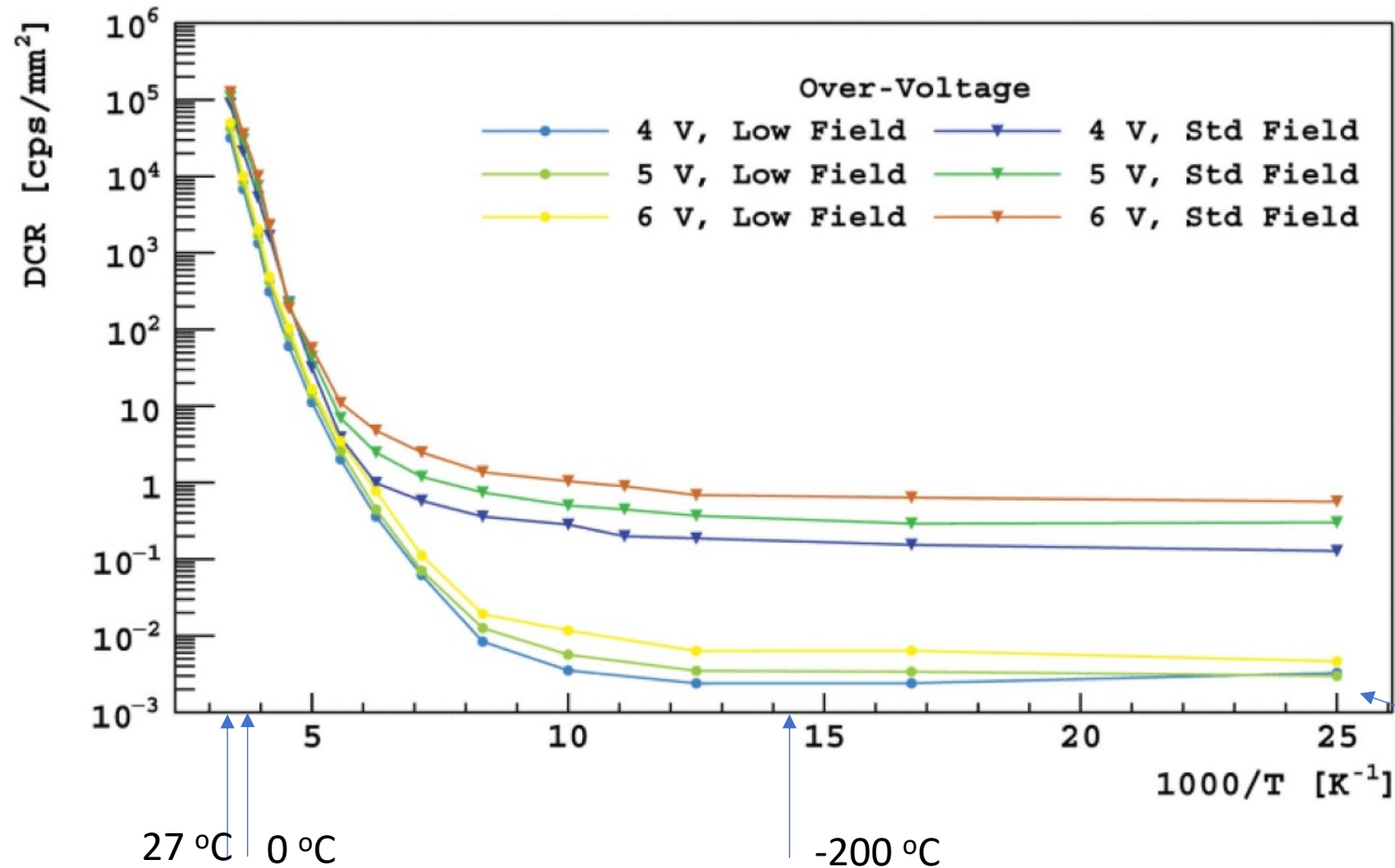
Direct CT immediately follow primary avalanche (same time but high ampl.)

Delay CT (few ns): secondary photons captured in neighbouring SPAD in non depleted region

AP: electron absorbed during avalanche, then released



SiPM: DCR and temperature (cryo)



Exponential decrease of DCR stops at cryo temperatures

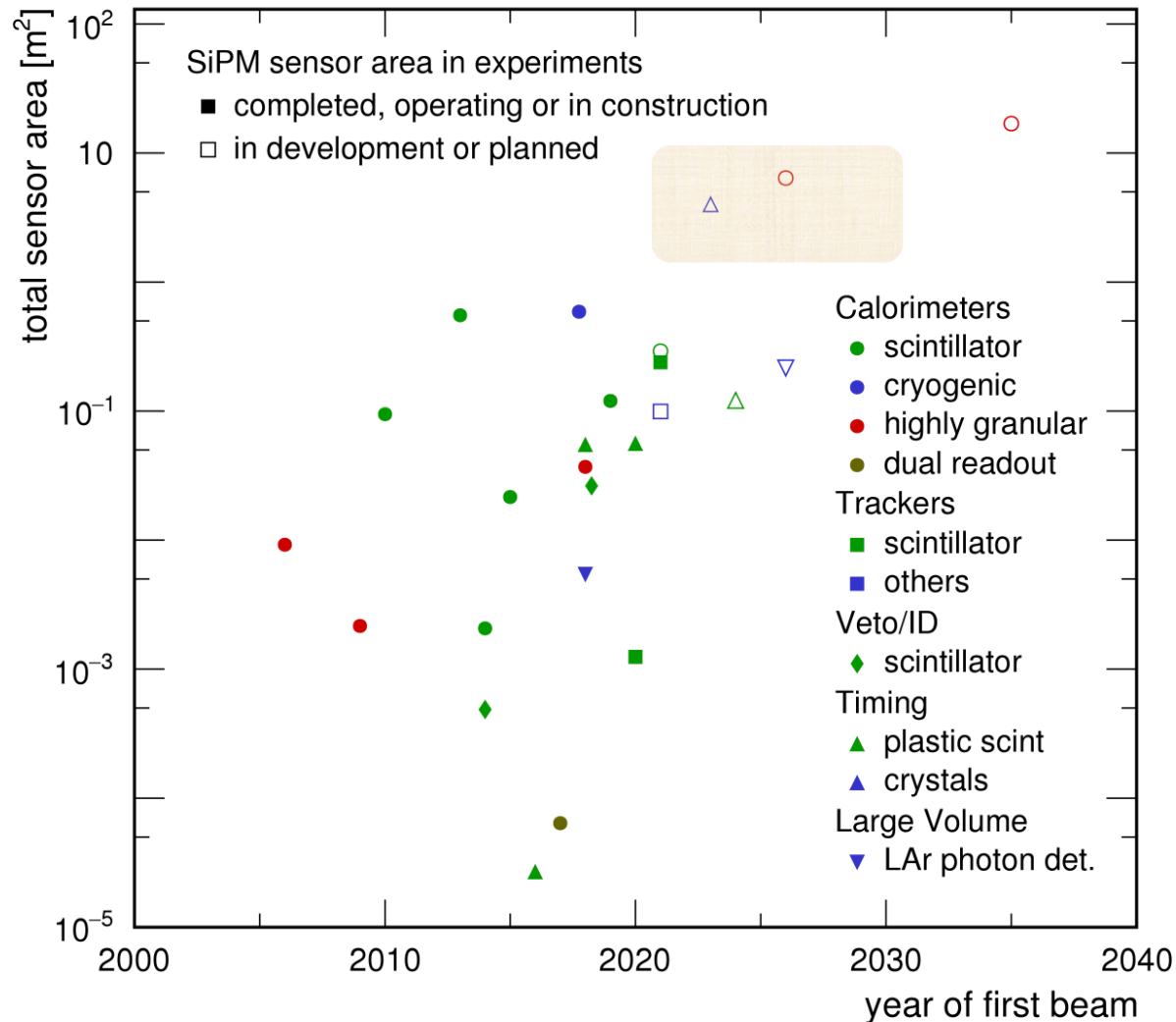
Remaining DCR is due to tunnelling effects and it is highly dependent on the electric field in the depleted region

Cooling can play key role in operating SiPM at low DCR!

NUV-HD-LF optimized for much lower DCR at 77K!
Reduction of AP probability

F. Acerbi et al, IEEE Trans. 64 (2017) 521

SiPM are now ubiquitous in HEP/NP/Astropart



F. Simon, NIMA 926 (2019) 85-100

SiPM are naturally attractive for HEP/NP

- Small size
 - High Photon-detection efficiency
 - Cheap
 - Insensitive to magnetic field
 - No high signal with MIP
 - High Gain
- Radiation tolerance
 - Finite dynamic range (depending on cells)
 - Temperature dependence of V_{bd}
 - **Dark Count Rate**


**Take home message*

Next generation: SiPM O(1-10 m²) area/detector

Review of recent SiPM for HEP applications

M. Bonesini et al.,

Nuclear Inst. and Methods in Physics Research, A 1047 (2023) 167903

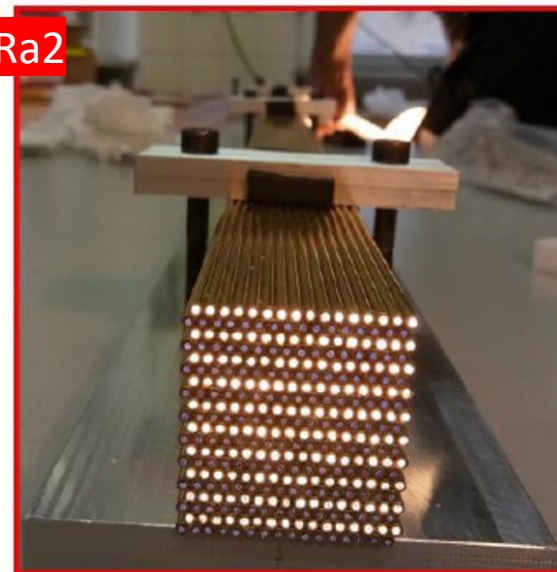
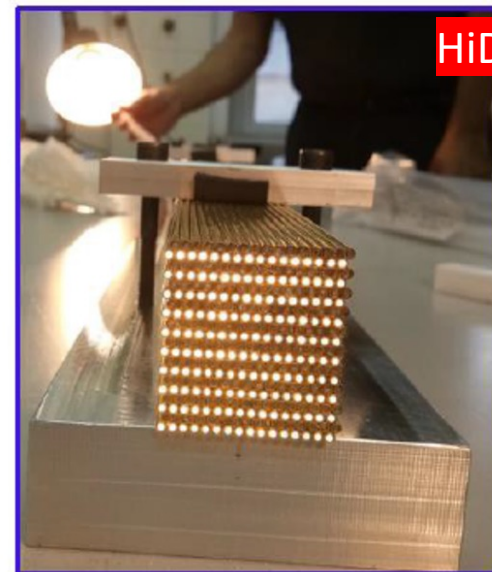
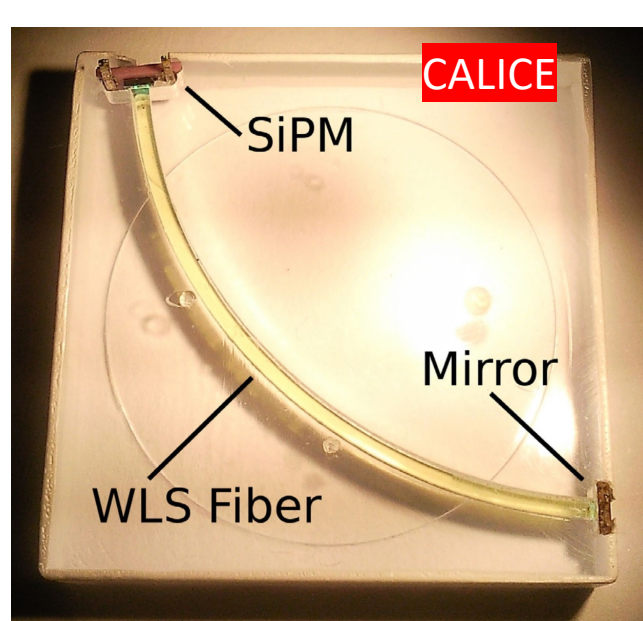
Example # 1: SiPM readout for calorimetry: from CALICE to Hydra2

Most common application of SiPM → Readout of organic/inorganic scintillators → calorimeters
 Geiger-mode + finite density → inherent saturation → compensation techniques to recover linearity

Detector	Year	Info	SiPM	SPAD μm
CALICE AHCAL	2004-2006	Hadron calo. 7608 photosensors "Demonstrator" WLS embedded in the tile. Coupling fiber-SiPM with air gap	MEPHi/CPTA 1x1 mm ²	32
T2K	2010	ECAL (and othe sub-systems; tracker, p0 detector, muon tracker) Track and shower resolution 1 ns https://arxiv.org/pdf/1308.3445.pdf	HPK S10362 1.3x1.3 mm ²	50
DREAM	2018	Dual Readout calorimeter "Demonstrator" // RD52 Cerenkov light yield measured twice w.r.t "PMT version" https://doi.org/10.1016/j.nima.2018.05.016	HPK S13615 1x1 mm ²	25
HiDRa2	2023+	Dual Readout calorimeter "Demonstrator". // AIDAInnova Recent development with high number of channels	HPK S16676 1x1 mm ²	10 15

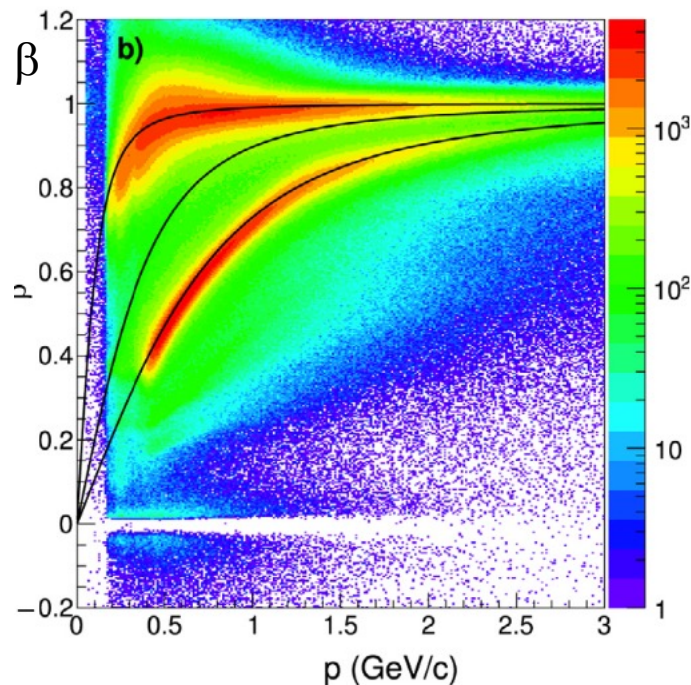

**Take home message*

- From pioneering times to baseline choice for future sophisticated calorimeter
- HPK sets the standard (and customises for HEP/NP)

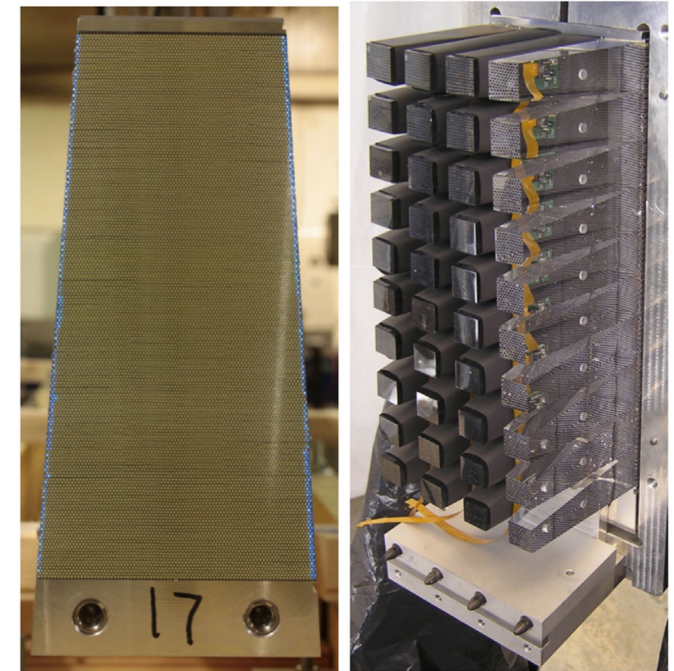


- 9 modules made of 16 x 20 capillaries (160 Cer and 160 Scint)
- capillaries (brass): 2 mm outer diameter and 1.1 mm inner diameter
- 81920 fibers (currently 10000 equipped with SiPM)

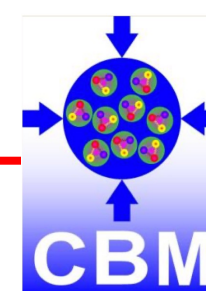
- 2013 → one of early SiPM adopters!
- barrel ECAL: photons from 50 MeV to several GeV / sampling calorimeter
- 3840 SiPM installed: 3x3 mm² / 16 channels 4x4 array
- Hamamatsu S12045(X) (SPAD 50x50 μm²)
- Energy resolution $\sigma_E/E = 5.2\%/\sqrt{E(\text{GeV})} \oplus 3.6\%$ comparable to KLOE (PMT based)



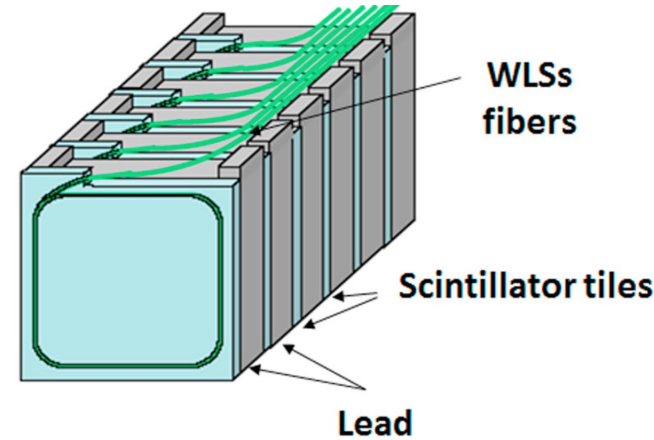
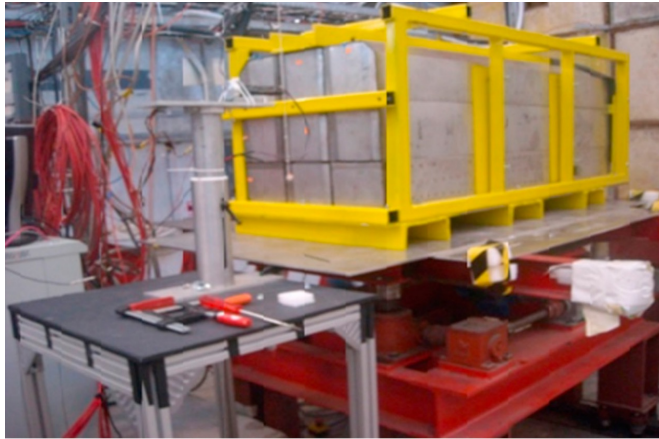
PID detector (TOF) given SiPM time resolution (150 ps)



Calorimeters with SiPM readout:



example



CBM Projectile Spectator Detector (forward hadron calorimeter)

N. Karpushkin et al., NIMA 936 (2019) 156

<https://doi-org.ezproxy.cern.ch/10.1016/j.nima.2018.10.054>

60 lead/scintillator layers \rightarrow WLS \rightarrow SiPM readout

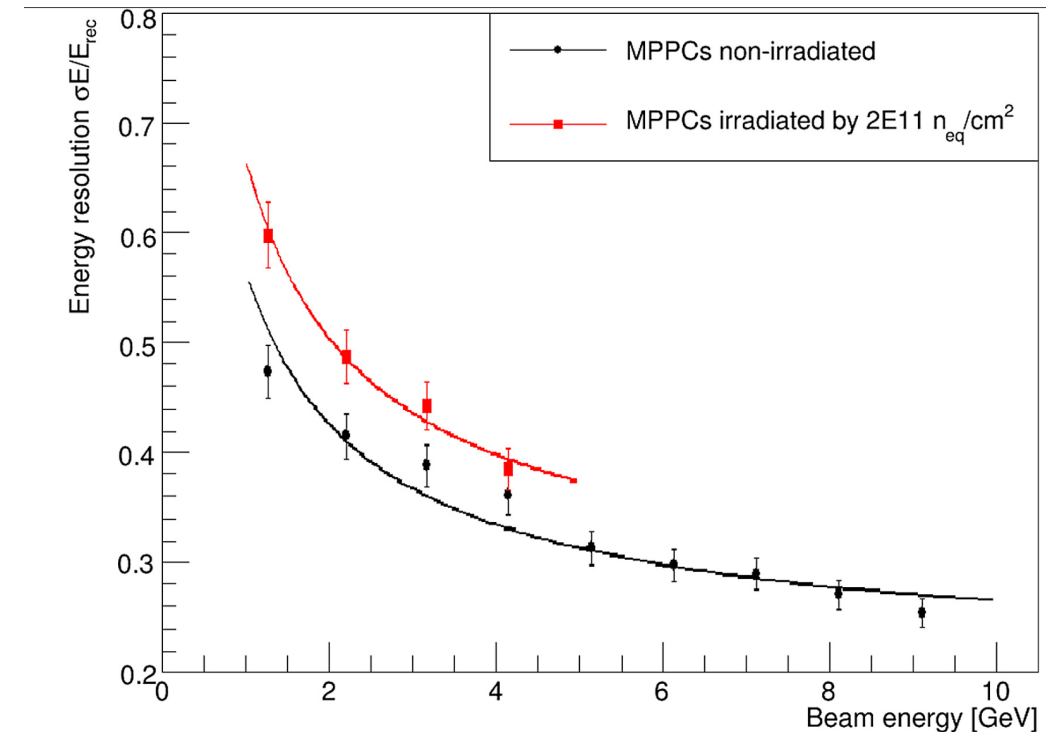
SiPM readout: MPPCs S12572-010P

radiation damage tested for SiPM



**Take home message*

**DCR increase normally manageable,
But impact on energy resolution must be studied**



Intermezzo: how much radiation damage?

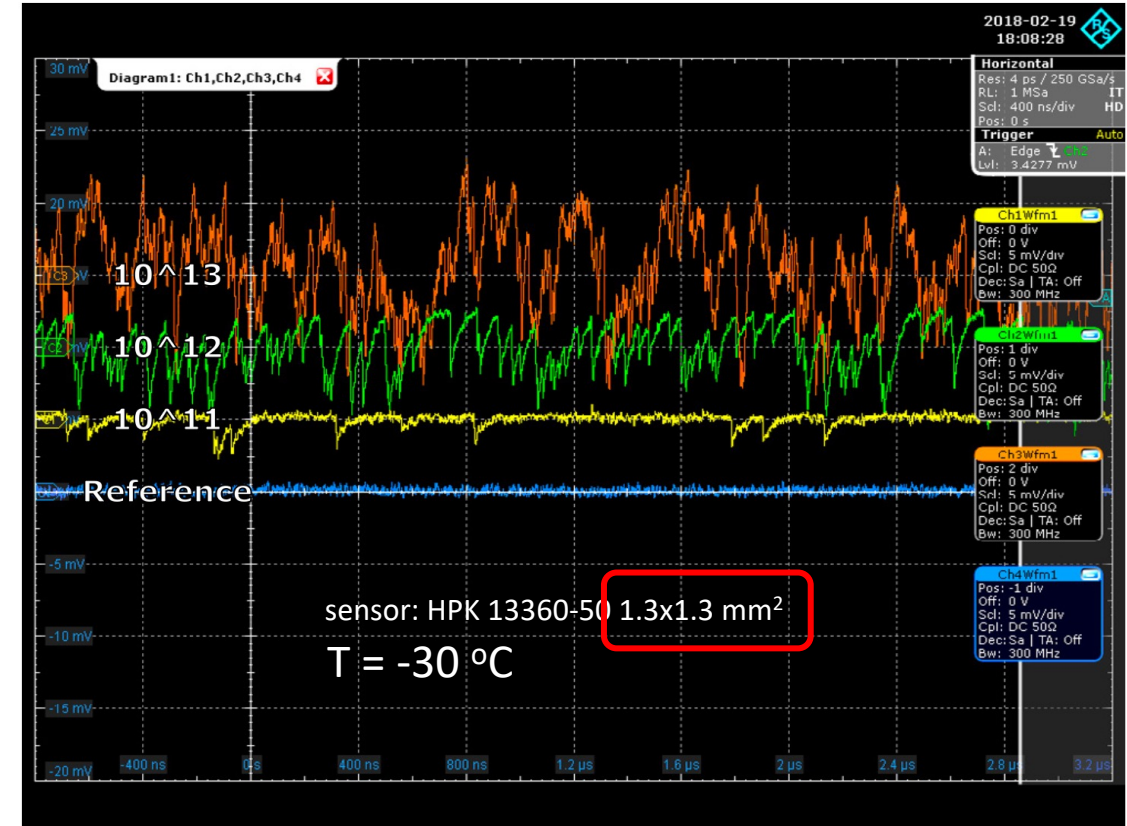
During last 10 years growing studies/ literature on SiPM radiation damage, see review from

[E. Garutti and Y. Musienko, NIMA 926 \(2019\) 69](#)

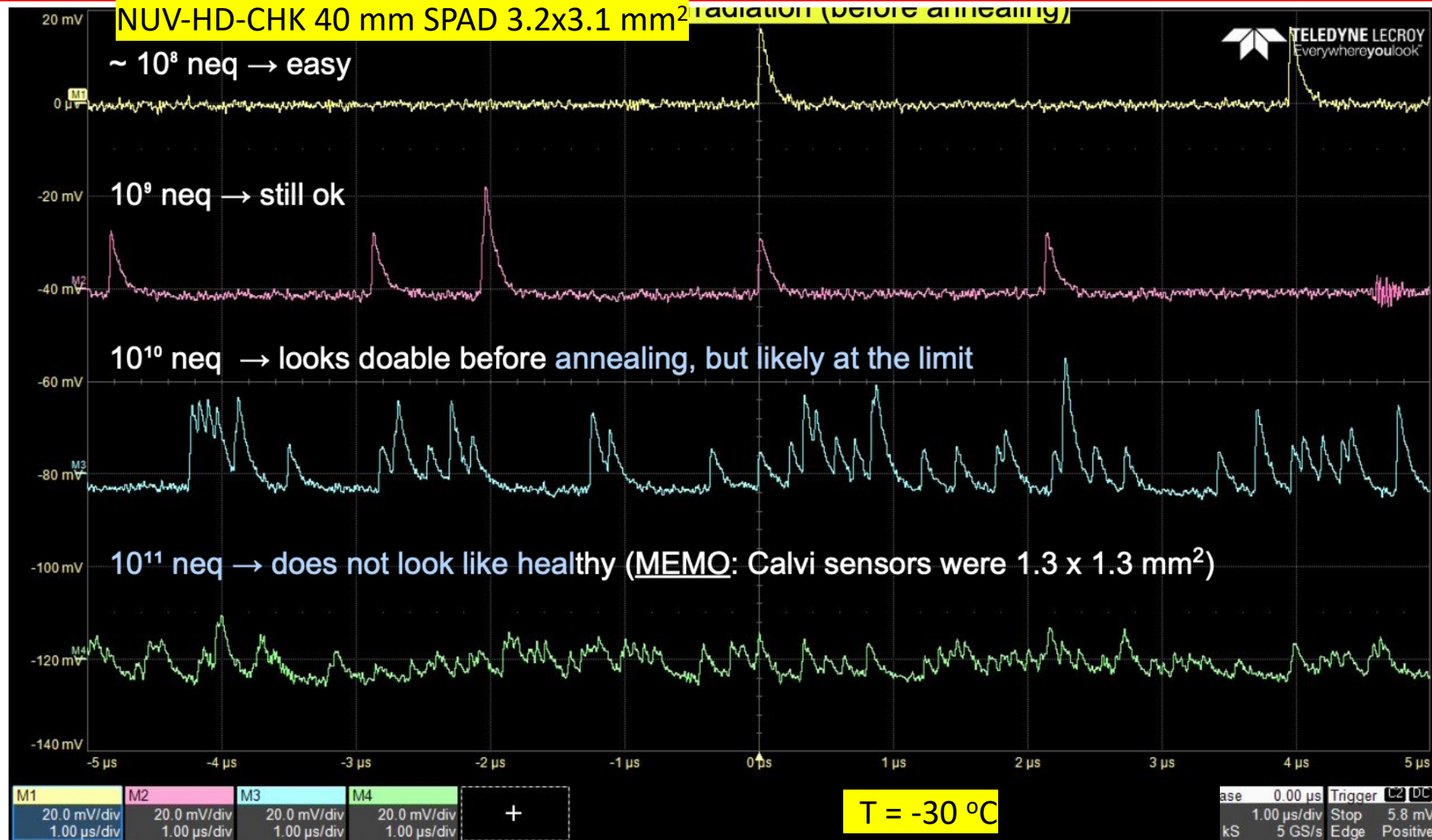
Up to 10^{11} 1-MeV n_{eq}/cm^2 radiation damages increase currents and DCR (and affects V_{bd}) **but the baseline is still there** (with proper cooling)

- For a calorimeter: how the damaged baseline spoils energy resolution and how affect efficiency
- For a RICH: can we maintain single photon detection, can we keep DCR “under control” to still get rings?

[M. Calvi et al., NIMA 922 \(2019\) 243](#)



And moving to 3x3 mm² SiPM...



10⁸ n_{eq} ok

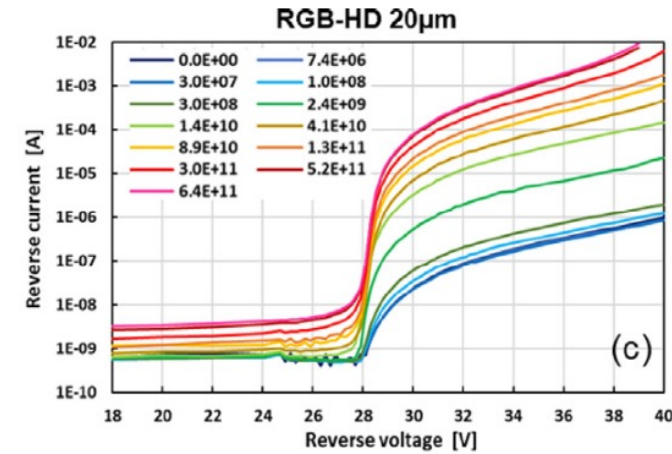
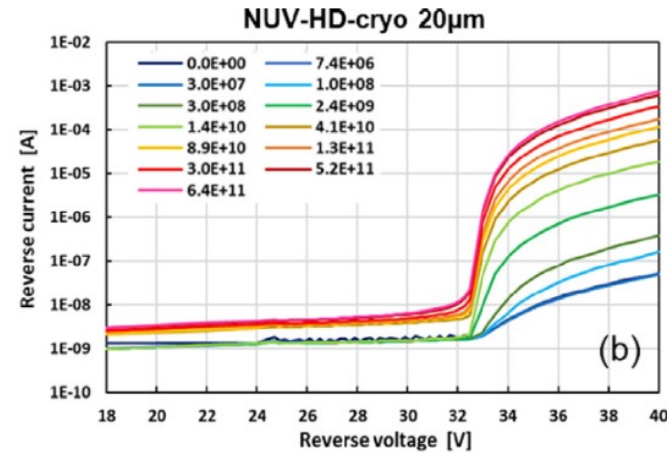
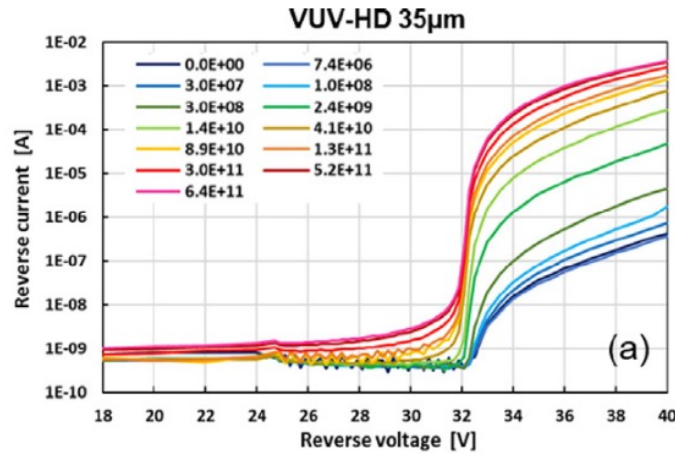
10⁹ n_{eq} still ok

10¹⁰ n_{eq} challenging

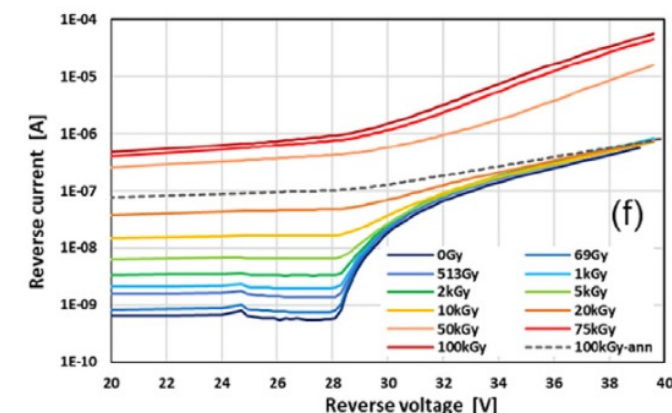
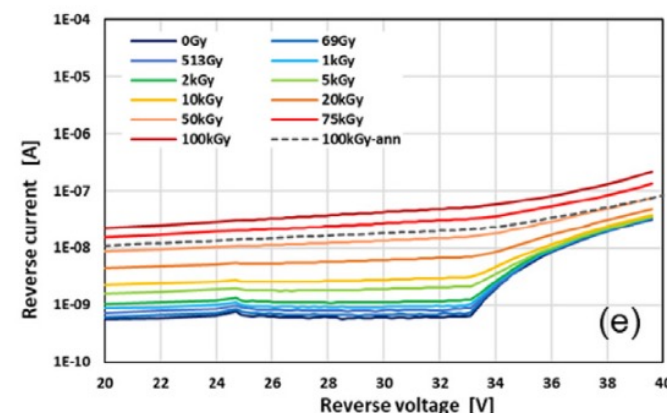
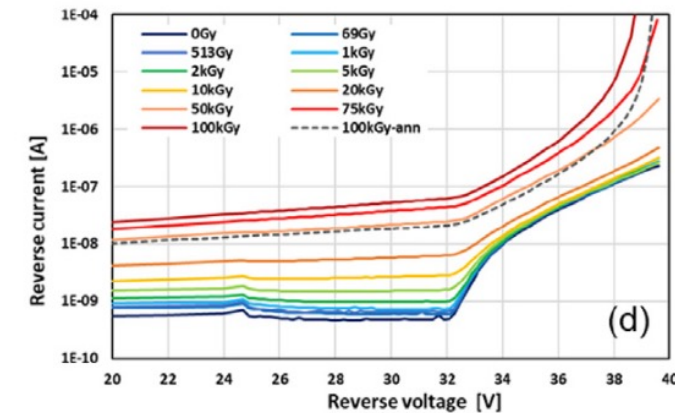
10¹¹ n_{eq} baseline lost

Radiation damage: impact on I-V curves

F. Acerbi et al, Nuclear Inst. and Methods in Physics Research, A 1047 (2023) 167791



proton fluences



doses (X-ray)

- neutron/proton → leakage current doesn't increase/dark current increase → damage in the bulk
- X-ray → leakage current increase → defects in the interface between dielectrics and silicon (including trenches)

How mitigate the radiation damage?

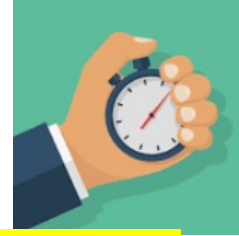


"DCR decreases by a factor 2-2.5 every 10 degrees"



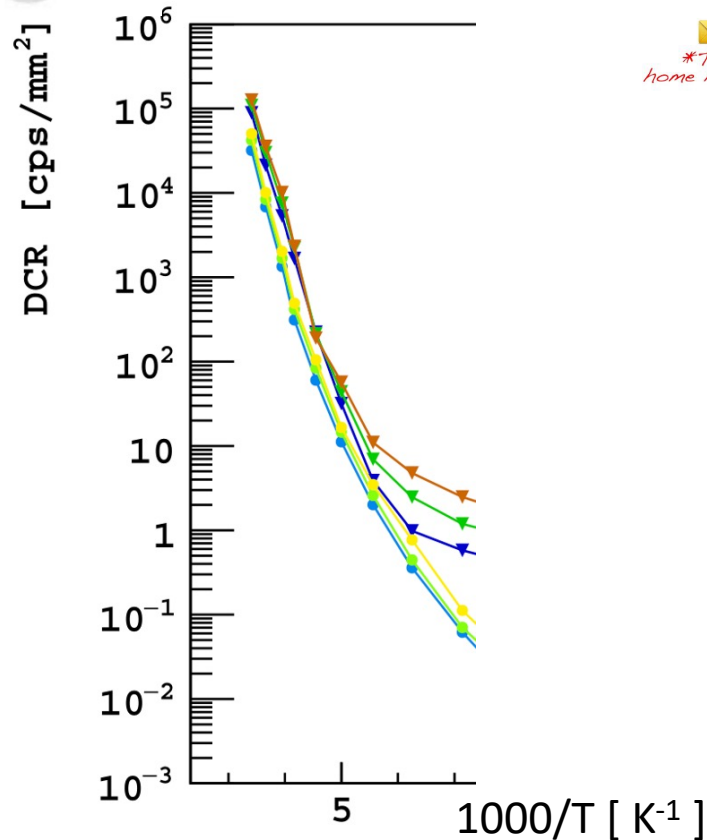
annealing

"DCR decreases by a **factor 20** after an annealing cycle up to 175 °C"



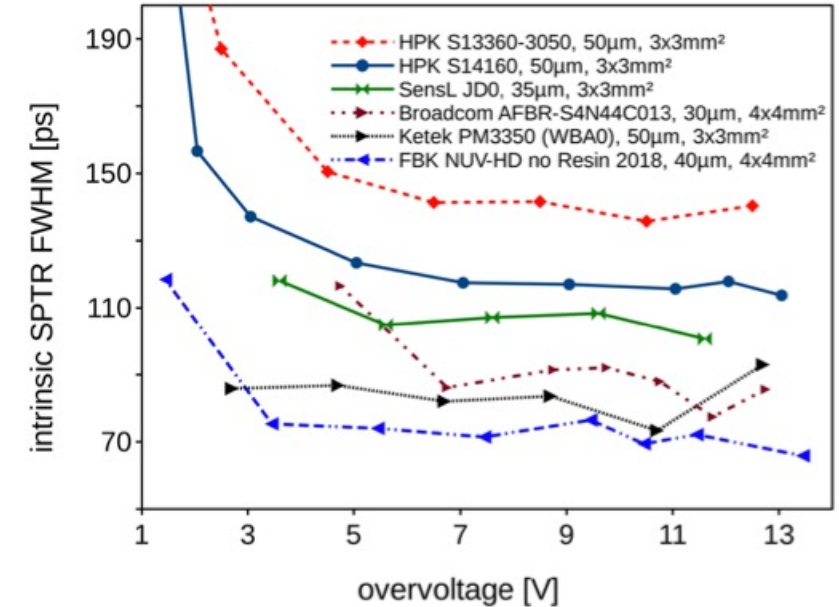
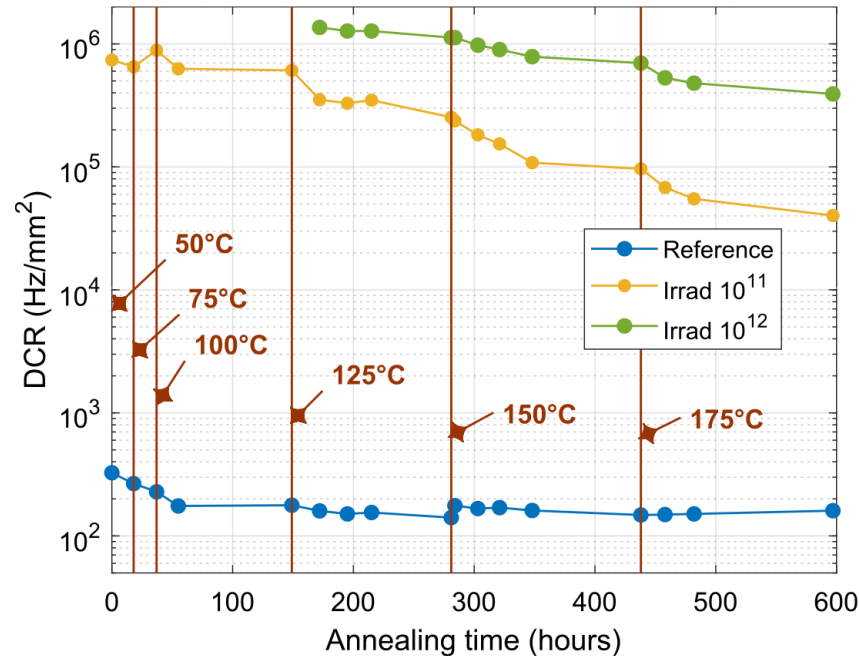
timing

- Timing resolution below 100 ps are nowadays achieved by SiPM
- A 3σ cut based on interaction time can reduce DCR ("time shutter on front-end electronics")



*Take home message

How, how often and where to anneal depend on the application



[Acerbi F. et al., IEEE Trans. On El. Devices 64 \(2017\) 521](#)

[M. Calvi et al., NIMA 922 \(2019\) 243](#)

[S. Gundacker et al., Phys. Med. Biol. 65 \(2020\) 025001](#)

cooling is critical in SiPM-based readout

P. Antonioli - SNRI

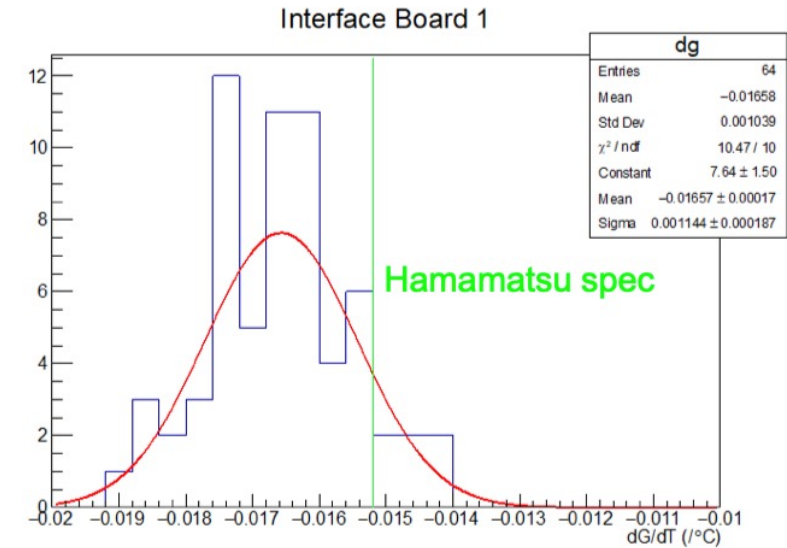
SiPM: temperature and gain

Important lessons learned by sPHENIX on:

- temperature dependence → cooling system
- radiation damage → small slow long term recovery at RT
- fluence expected 10^{11} n_{eq}/cm^2



Gain Temperature Coeff dG/T ($\%/^{\circ}C$)



EMCAL Cooling System

SiPM Loop
Sector 1



**Take home message*

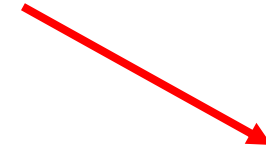
in SiPM business cooling is not just about DCR decrease or mitigation of radiation damage

SiPM for PID

Three broad categories here for SiPM use:

1. plastic-scintillator based (charged particle/showers) → scintillation light
2. Detection of Cerenkov light (RICH)
3. Time-of-flight detectors

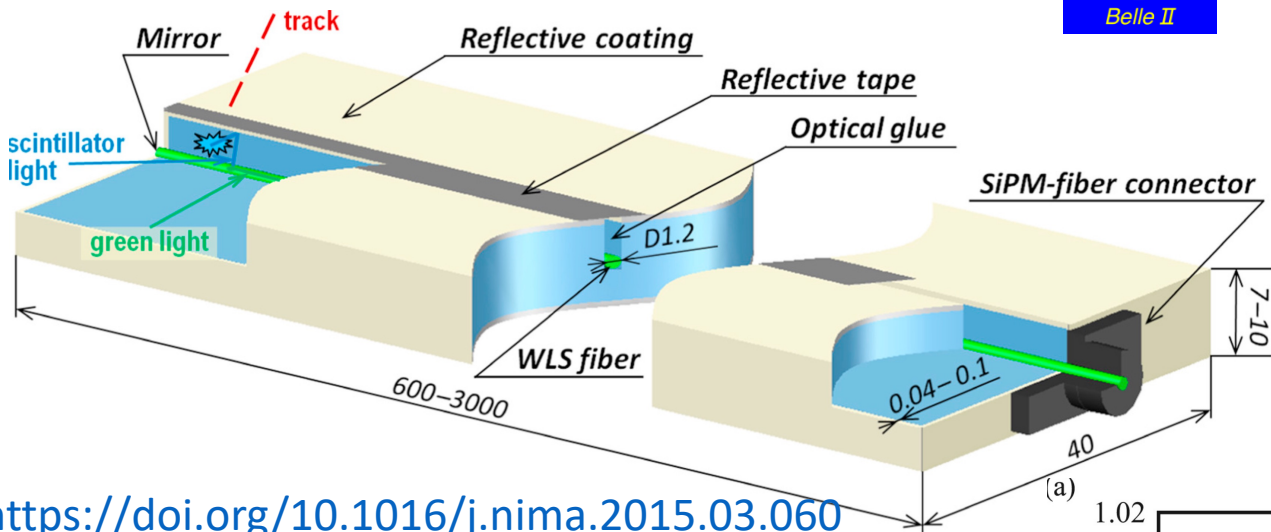
“similar” to calorimetry



Not realized so far, it could be
at reach within next 10 years

Examples of PID/veto with scintillation light

EKLM detector @ Belle II for K_L and muon

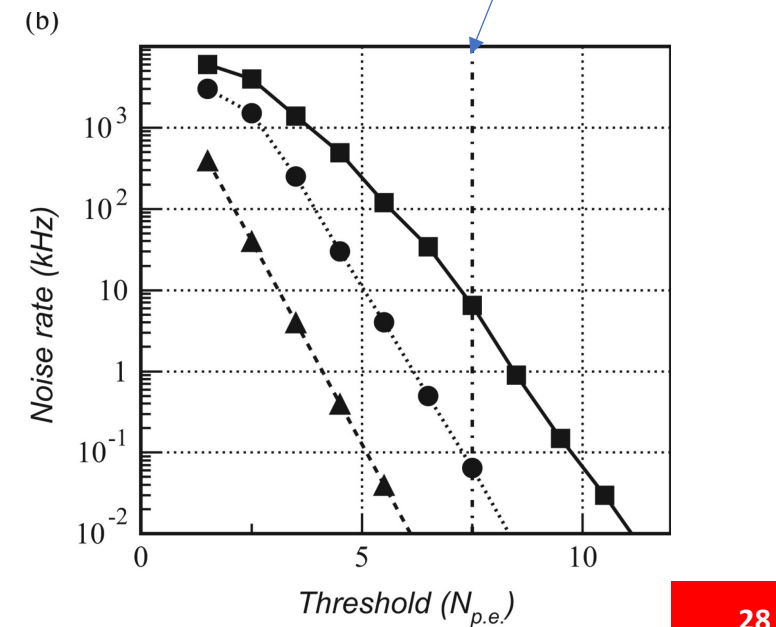
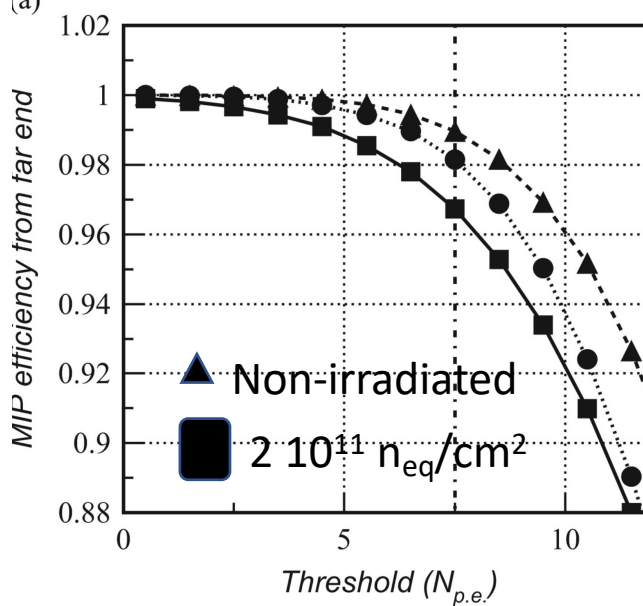


- Alternating layers of active scintillator and 4.7 cm thick iron plates
- SiPM choice strategic (no PMT due to magnetic field)
- CPTA / Hamamatsu choice done based on radiation tolerance studies
- **The difference between the Hamamatsu and CPTA mainly due to different thicknesses of the sensitive zone and the difference in manufacturing details (purity of the raw materials and also of the SiPM surface [→ impact on "starting dark noise"]**

<https://doi.org/10.1016/j.nima.2015.03.060>

3.9 interaction length $\rightarrow K_L^0$ can shower hadronically \rightarrow muon separation

Note RPC were replaced due to "fake showers" generated by neutrons. DCR increase due to neutrons in SiPM under control!



RICH with SiPM based readout?

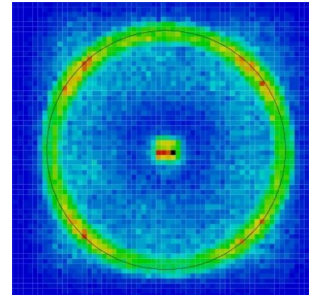
So far not realized

Pioneering work during Belle II Upgrade studies

P. Križan et al. NIM A594 (2008) 13

<https://doi.org/10.1016/j.nima.2008.05.040>

<https://doi.org/10.1016/j.nima.2008.07.013>



CAVEAT:

pioneering work for BelleII was done with (now obsolete, noisy and out-of-market) Hamamatsu MPPC S10362-11-100P

Main reference: a recent (2020) review exactly on this topic:

<https://doi.org/10.1016/j.nima.2020.163804>

S. Korpar, P. Križan. "Solid state single photon sensors for the RICH application"

As potential detectors were listed here:

- HELIX
- LHCb RICH1 Upgrade 2
- RICH for a SuperCharm-Tau factory (21 m²)
- BELLE II ARICH
- EIC RICH
- (now → ALICE 3 RICH)

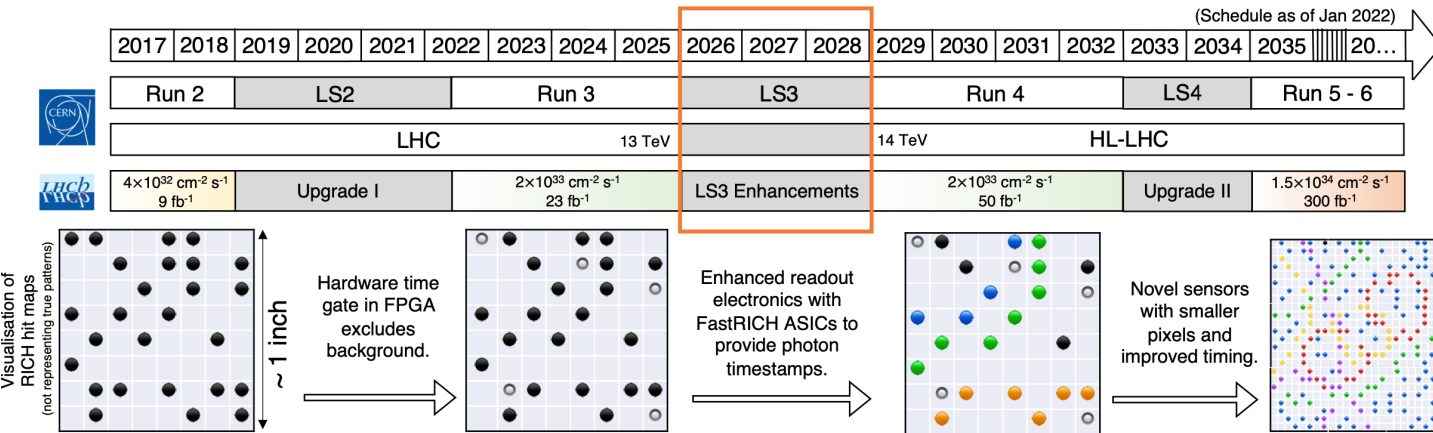
7. Summary

Semiconductor sensors for single photons, in particular SiPMs, are a novel device for RICH. Their advantages, operation in the magnetic field, high quantum efficiency, low supply voltage, fast response, flexible granularity, make them an almost ideal sensor for ring imaging Cherenkov detectors. The main challenge, a high occupancy due to dark counts, can be overcome by a narrow time window and by using light collecting elements to increase the ratio of the light collection area and the SiPM sensor area. The remaining issue for operation in experimental environments with high radiation exposure, in particular by neutrons, is under intense study for the next generation of experiments.

LHCb RICH plans

Evolution of the RICH photon detector

Relatively long period of LS3 central to the RICH evolution.



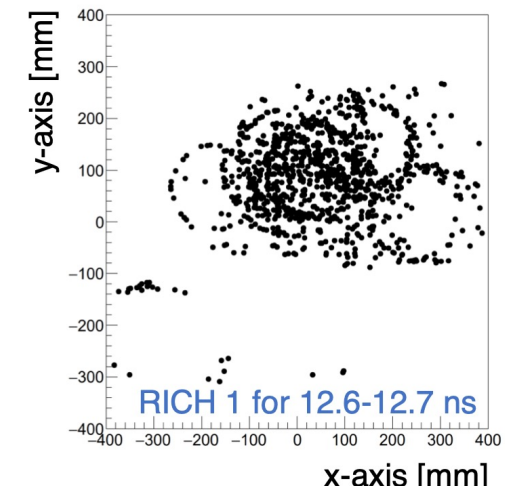
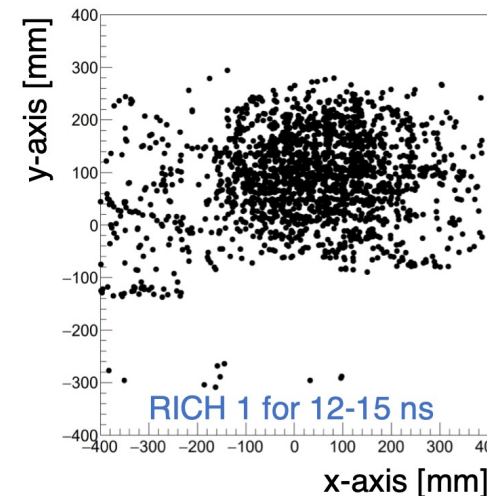
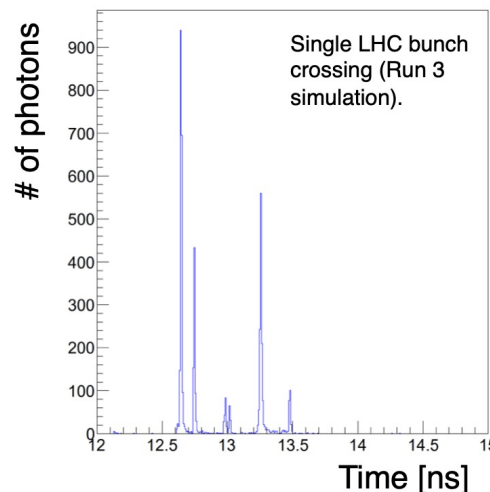
(Since RUN3 → MaPMT as photosensors)
As photosensors in RUN5 @ LHCb
SiPM: [R. Cardinale @RICH2022](#)
LAPPD: [F. Oliva @RICH2022](#)
are being considered

➤ LS3 / Run 4 : focus on **FastRICH** readout electronics with fast timing and wide input dynamic range.

➤ LS4 / Run 5 : focus on **sensor technology**. Fast-timing is essential for the luminosity challenge after Upgrade II. [1]

To reduce background and improve PID, need to accurately predict **when** the photons from a given track ought to arrive.

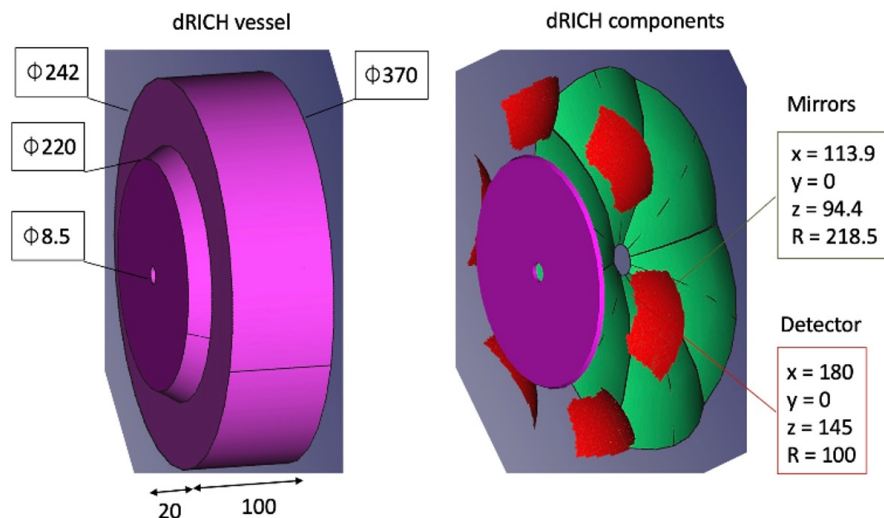
Fast switching electronics will be key for RICH SiPM based readout



- radiators: Aerogel ($n=1.02$)/ Gas ($n=1.0008$)
- 3 m^2 area, $3 \times 3 \text{ mm}^2$ pixel

inside magnetic field ($\sim 1 \text{ T}$)
 SiPM as baseline sensor

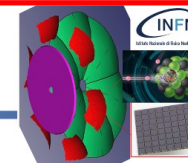
A SiPM readout for a RICH detector?



Silicon photomultipliers

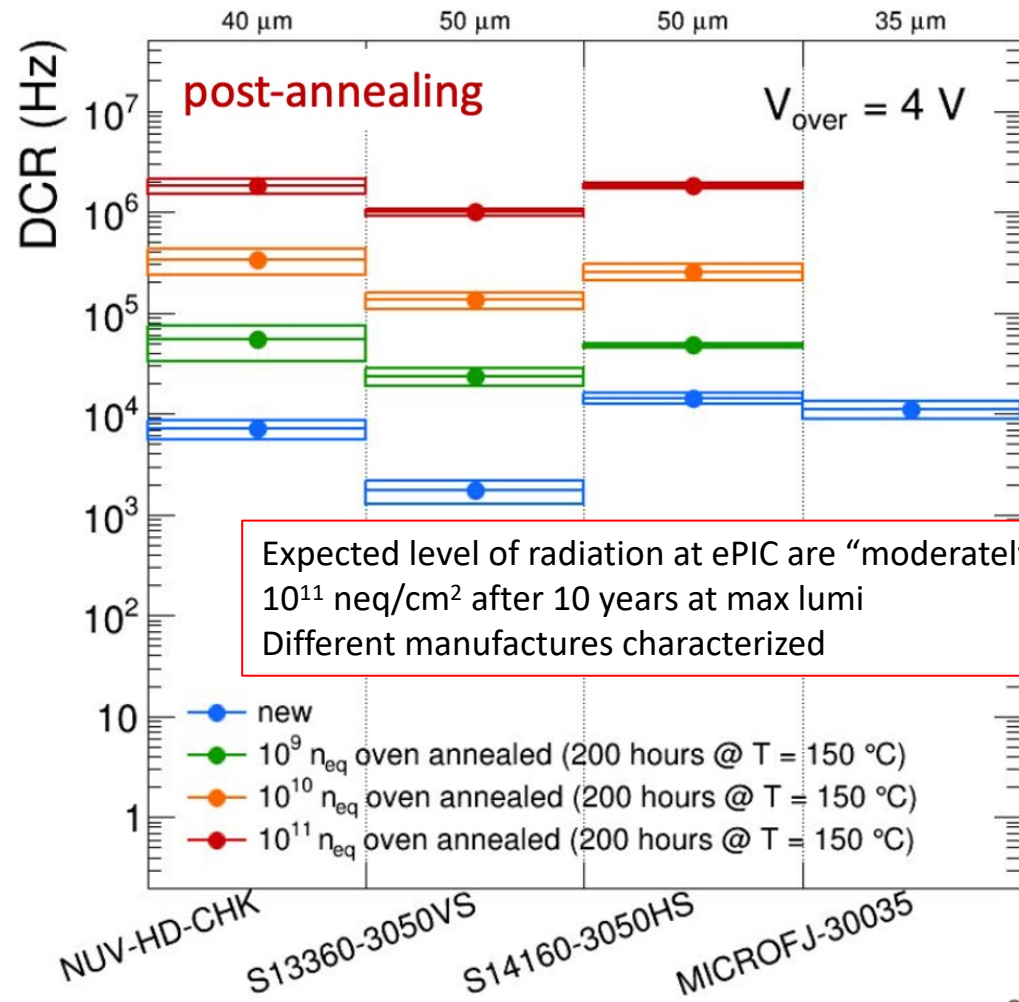
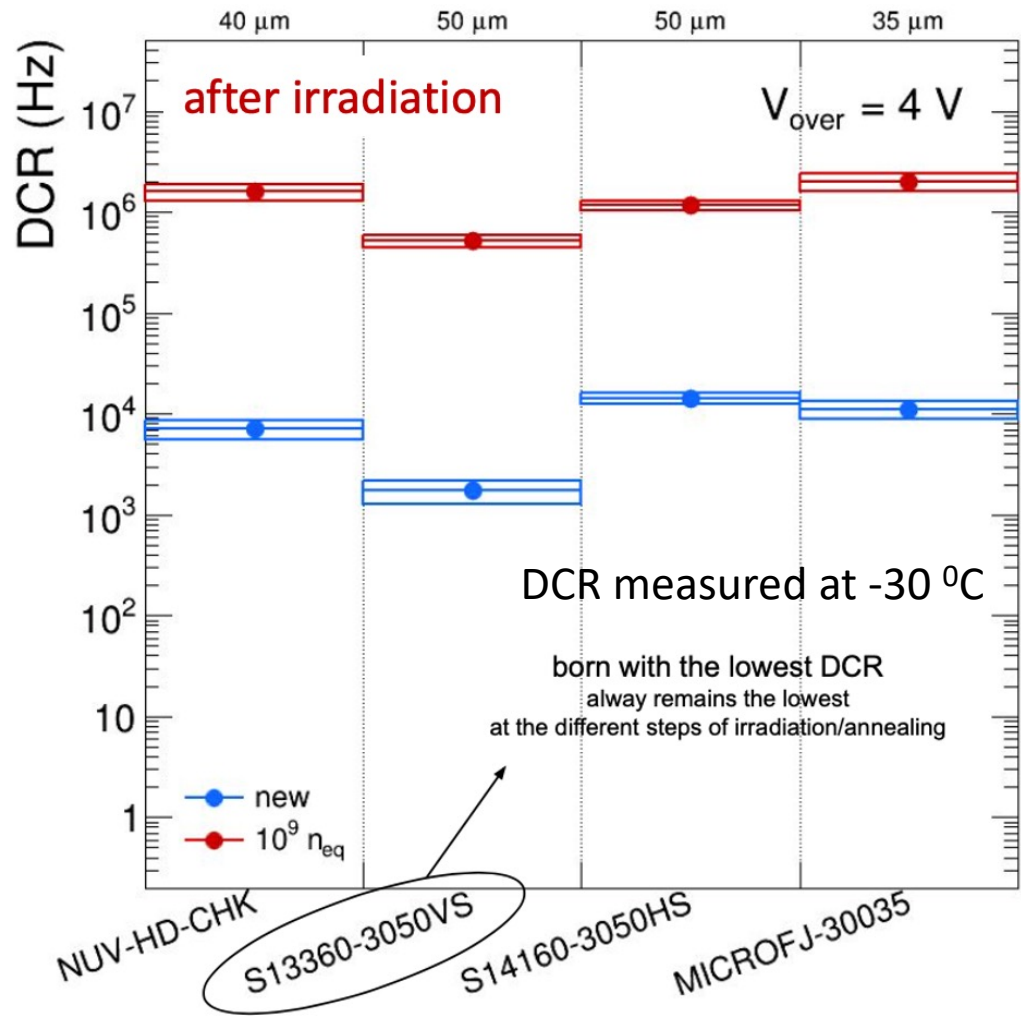
- ✓ Insensitive to magnetic field
- ✓ Cheap / Integrated arrays
- ✓ Time resolution within requirements ($< 200 \text{ ps RMS}$)
- ✓ Commercially available

- ? Single Photon resolution needed!
- ? DCR vs temperature \rightarrow cooling
- ? Not radiation tolerant: DCR increases!

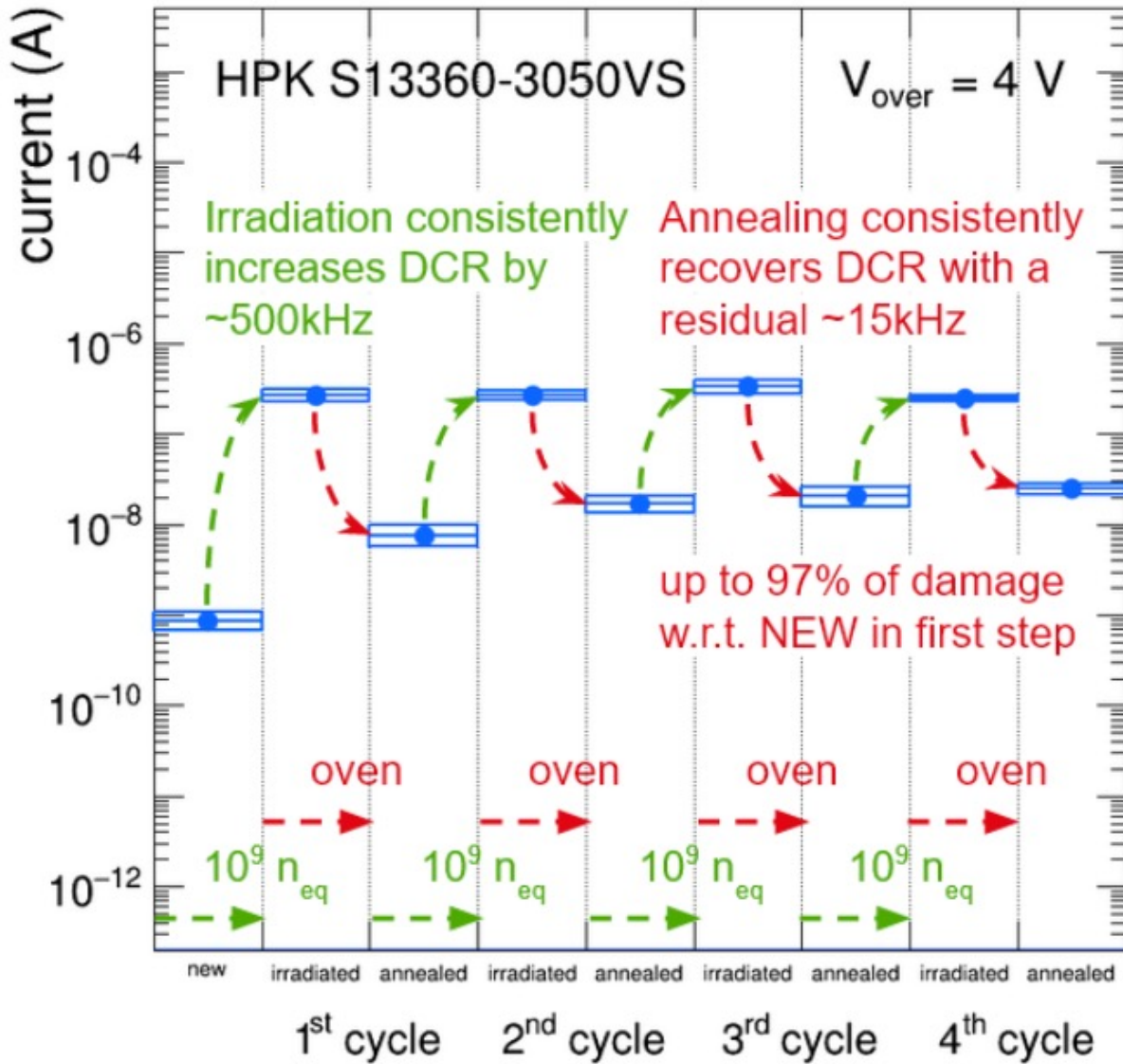


[PA @ CPAD Workshop 2022](#)

- Our R&D:** evaluate radiation tolerance and mitigation procedures (annealing)
- \rightarrow test large O(10-100) samples of different commercial (HPK/OnSemi) and prototypes (FBK)
 - \rightarrow establish annealing protocol, evaluate DCR after repeated annealing cycles
 - \rightarrow characterize sensors and test them on beam conditions
 - \rightarrow use/test realistic readout with ALCOR ASIC



O(10) DCR recovery post-annealing

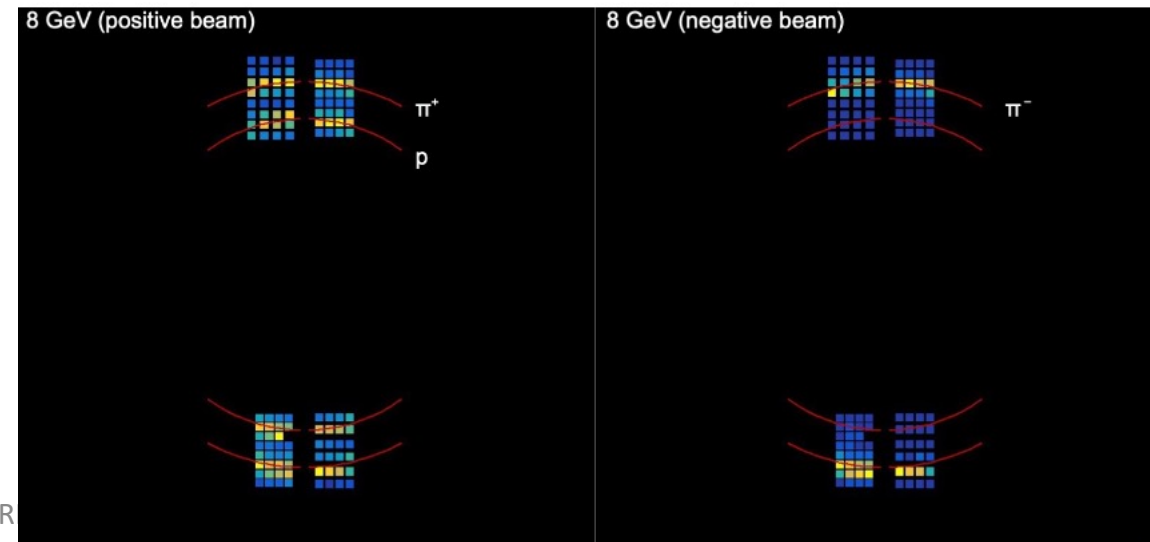


Novelty here:

- test reproducibility of repeated irradiated/annealing cycles on the same sensors.
- each shot is $10^9 n_{eq}$ (remember: 0.2/1 year EIC at max lumi)
- extract parameters (sensor and V_{over} specific!) to shape annealing cycles in the experiment
- Ring structures detected correctly at test beam with (irradiated + annealed) sensors

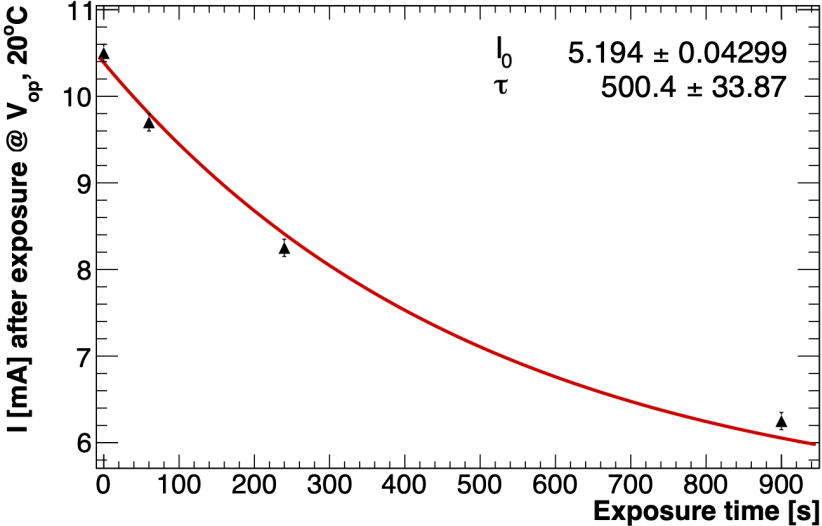
✉
*Take home message

no show stoppers so-far. Annealing “in-situ” with full-fledged prototype is next step!



Thermally vs electrically induced annealing for SiPM

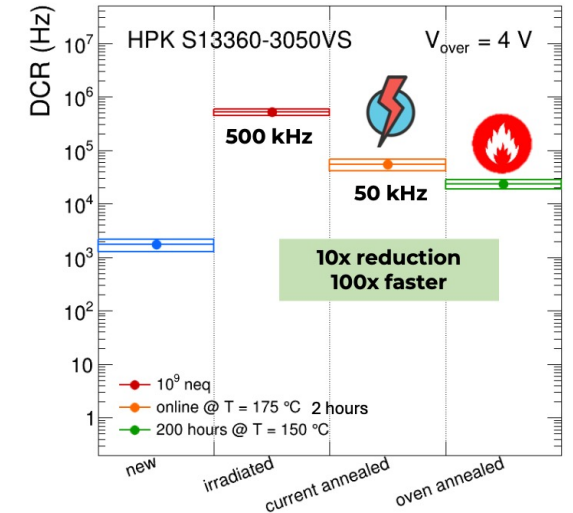
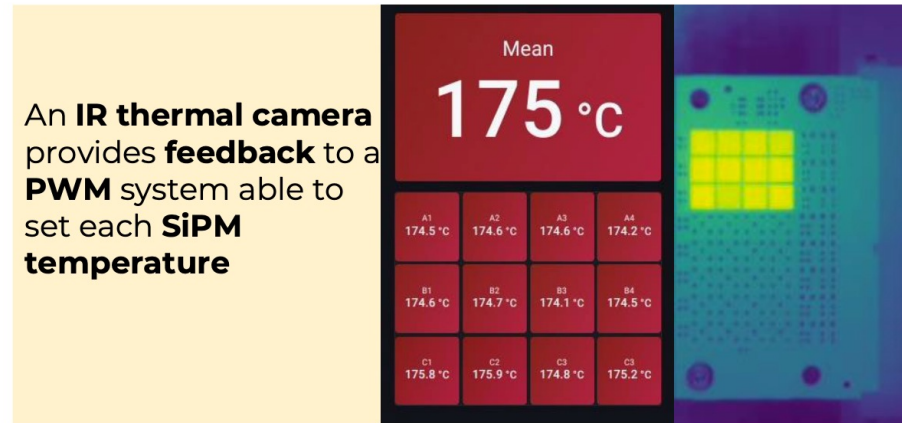
L. Rignanese @ [TWEPP-23](#)



Current annealing

Another way to heat up the sensors is by directly polarization. Current flowing into the SiPM, generates heat resulting in annealing. 175° C can be obtained providing 10 V and ~100 mA (~ **1 W**) per sensor @ room temperature

[M. Cordelli et al 2021 JINST 16 T12012](#) results on HPK and SensL (OnSemi) sensors, both forward and inverse bias



This opens up to "in-situ" annealing

Measurements taken @ $-30^\circ C$

Luigi Rignanese rignanese@bo.infn.it

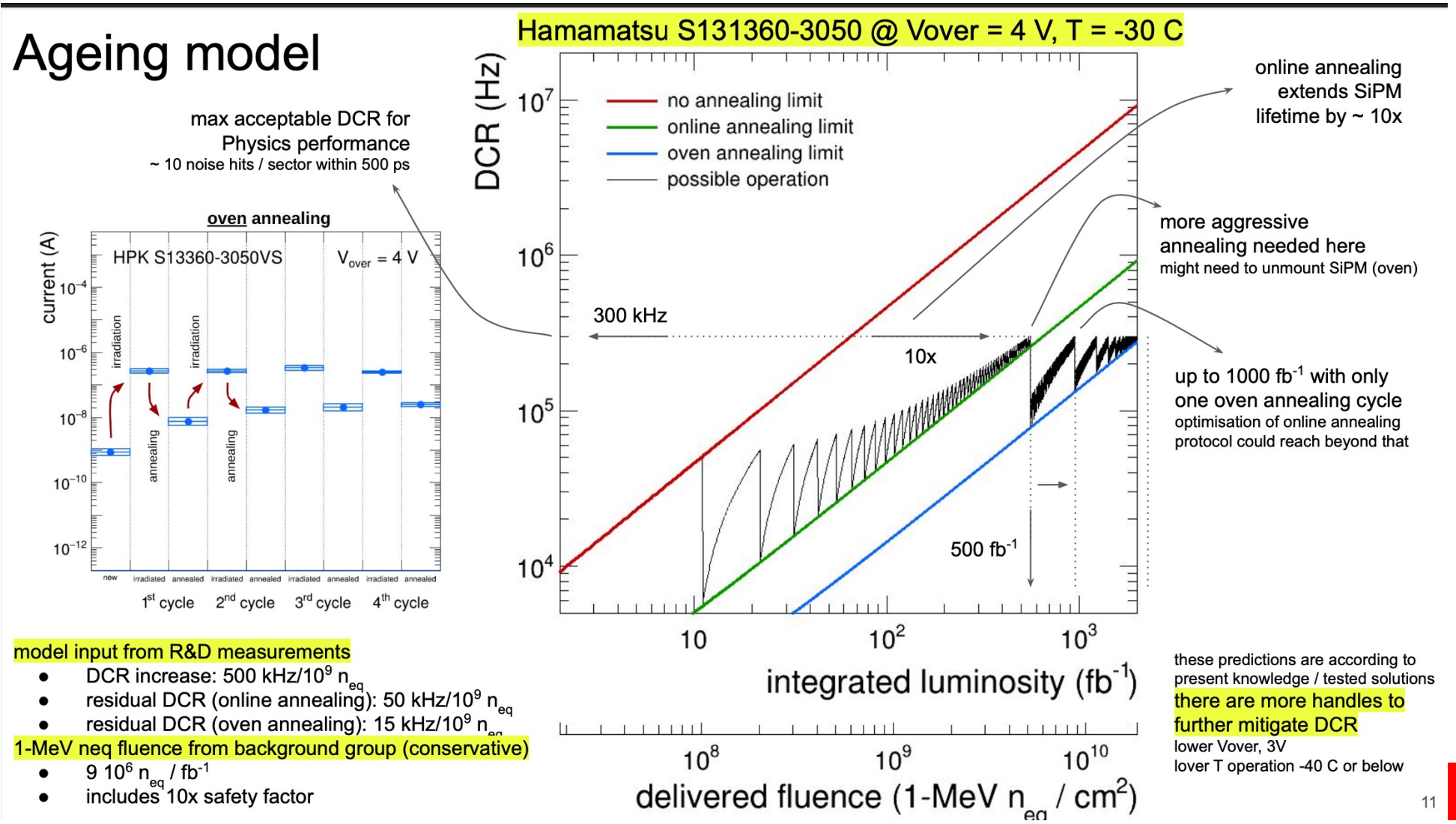
Modeling damaging & recovering

- extract parameters (sensor and V_{over} specific!) to shape annealing cycles in the experiment:
 - f_d : every 10^9 n_{eq} increases by 500 kHz DCR pixel rate (3x3 mm²)
 - f_a : each annealing leaves 15 kHz of additional DCR rate

$$DCR_r(k) = DCR_0 + f_d + (k - 1)f_a$$

DCR after k irradiation and k-1 annealing cycles

- damage and recovery remain additive
- annealing repairs f_a/f_d of a given sensor (97% here)

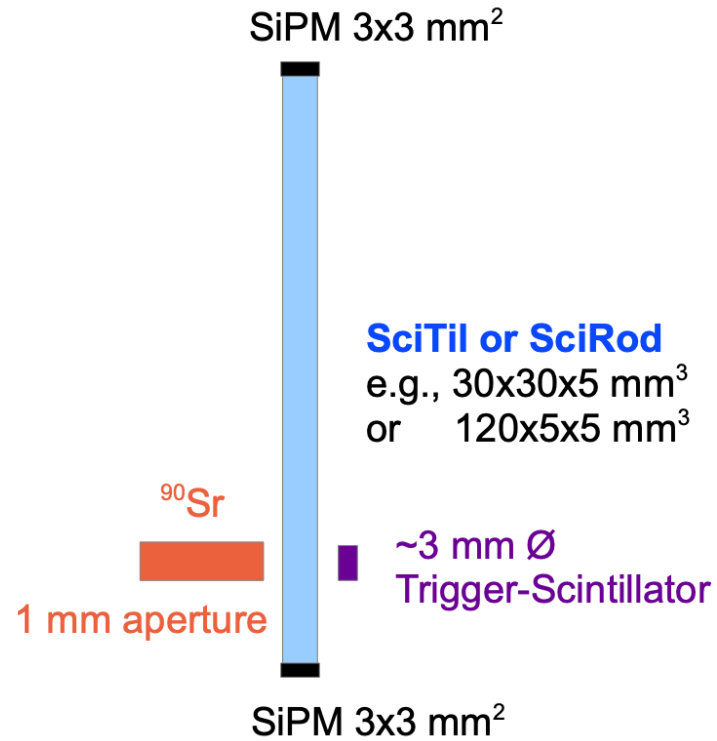


Next step: TOF + RICH with SiPM?

- traditional TOF system & SiPM
- MIP detection?
- TOF + RICH?

TOF SiPM based readout: example

Scintillator light → SiPM

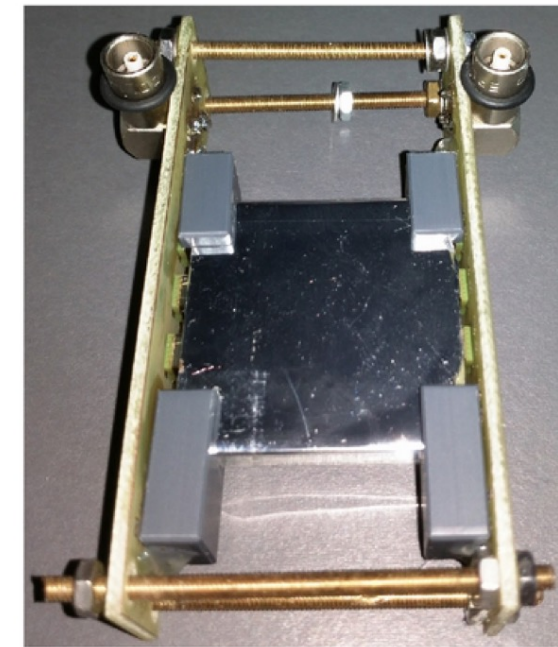
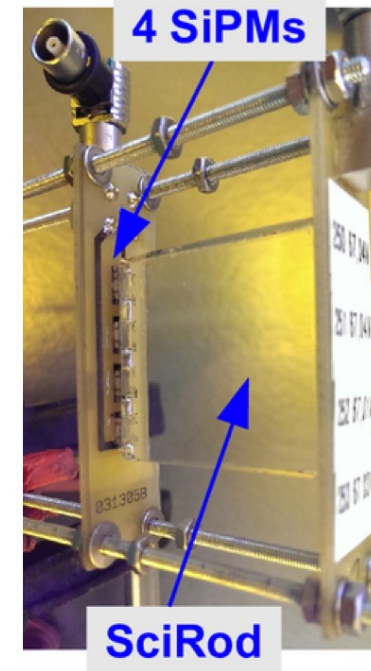


M. Böhm et al 2016 JINST 11 C05018
Hamamatsu S12652-050C MPPC
KETEK PM3350TP-SB0


**Take home message*

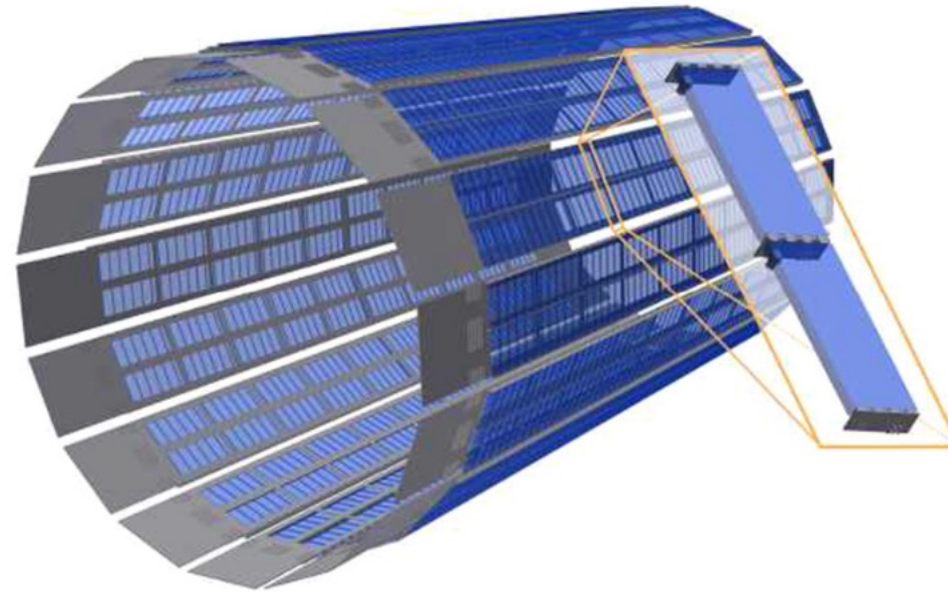
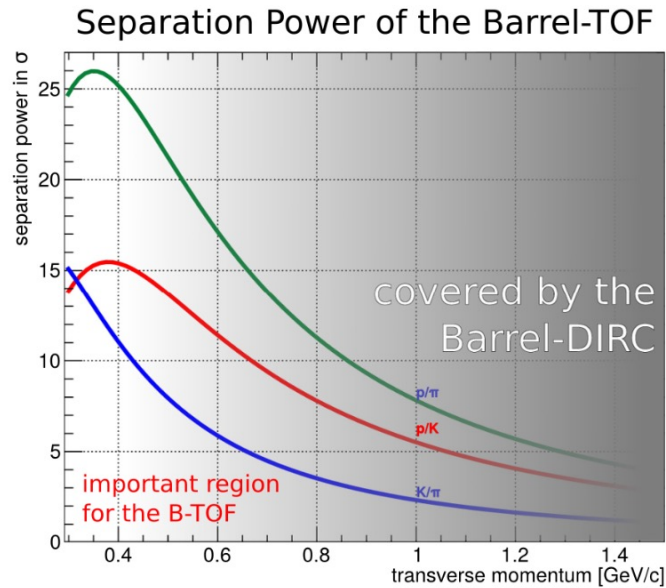
Design optimization for TOF SiPM based readout
scales with $N_{ph.}$ → serial connection

- Several optimization in design reported
- a) geometry of scintillator tiles
 - b) wrapping in aluminum foil
 - c) **read out by four SiPM serially connected**



resolution improves from 110-180 ps to 45 ps

TOF SiPM based readout: example



HPK S13360 currently indicated as selected SIPM in PANDA TDR with 50-60 ps resolution

https://panda.gsi.de/system/files/user_uploads/ken.suzuki/RE-TDR-2016-003_0.pdf

<https://doi.org/10.1016/j.nima.2018.11.094>

PANDA identifies hybrid mode

→ parallel connection for V_{bias}

→ series for signal with decoupling capacitor

Note AMS-100 for its TOF using PANDA approach + HPK S14161 reaches below 40 ps (with ^{90}Sr)

Instruments **2022**, 6(1), 14

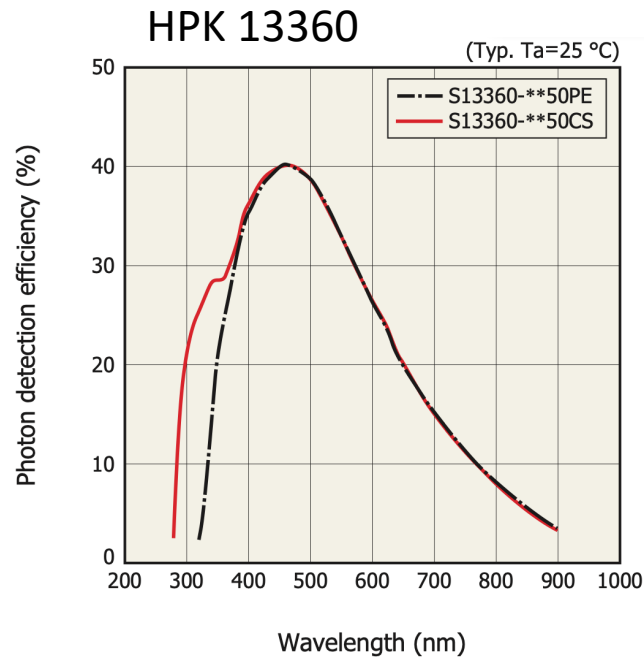
Intermezzo: basics of TOF scint+SiPM readout

$$\sigma_t^{ph} \propto \sqrt{\frac{\tau_r \tau_d}{N_{det}}} \propto \sqrt{\frac{\tau_r \tau_d}{N_{ph} \cdot \underbrace{QE \times FF \times P_G}_{\text{PDE}}}}$$

scintillator rise and decay time
number of detected photons

"scintillator quality"

Quantum Efficiency x Fill Factor x Geiger probability
(+ DCR) --> SiPM quality

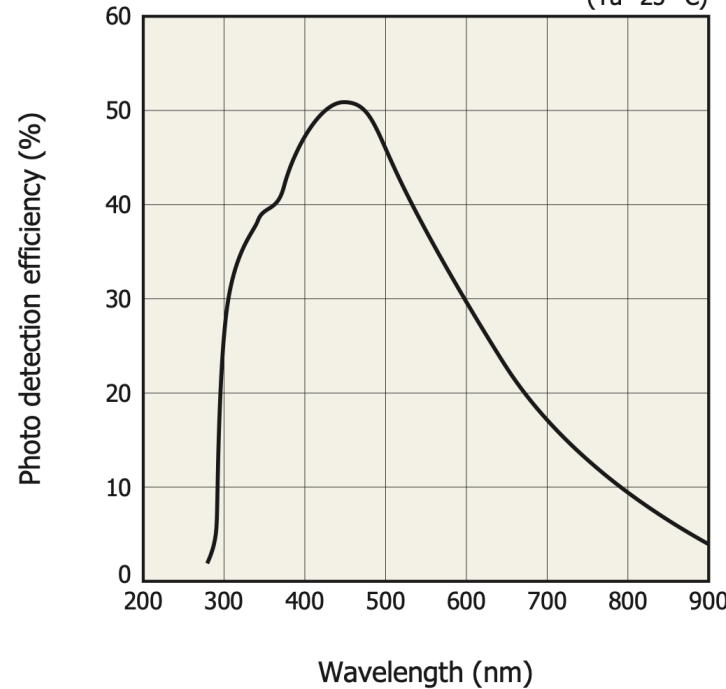


https://www.hamamatsu.com/content/dam/hamamatsu-photonics/sites/documents/99_SALES_LIBRARY/ssd/s13360_series_kapd1052e.pdf

PDE

HPK 14160

(Ta=25 °C)



Wavelength (nm)

P. Antonioli - SNRI

S14 w.r.t. S13 a higher PDE (50%
at $\lambda_{peak}=450$ nm, $V_{bias}=V_{BD}+2.7$ V)
lower crosstalk, a higher gain $O(10^6)$
lower breakdown voltage ($V_{BD}=38$ V).

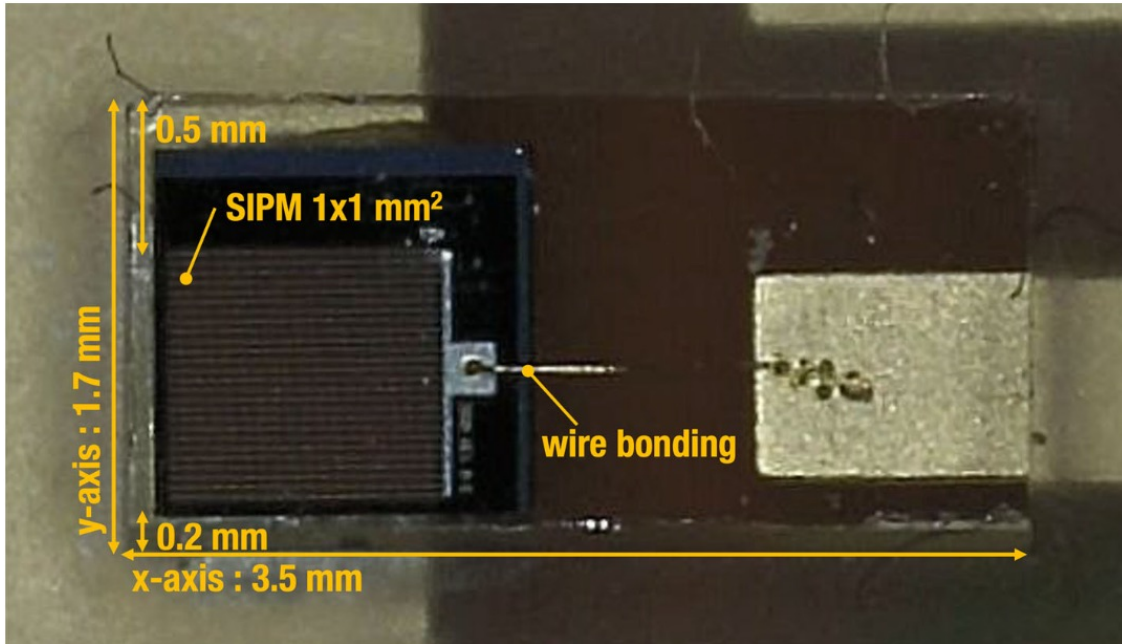
S14 w.r.t. S12 : afterpulse and DCR reduced by
two orders of magnitude



commercial solutions have progresses
faster than experiment life-cycle (from
TDR to commissioning)
It is a usual challenge, but may be
particularly acute in this field

https://www.hamamatsu.com/content/dam/hamamatsu-photonics/sites/documents/99_SALES_LIBRARY/ssd/s14160_s14161_series_kapd1064e.pdf

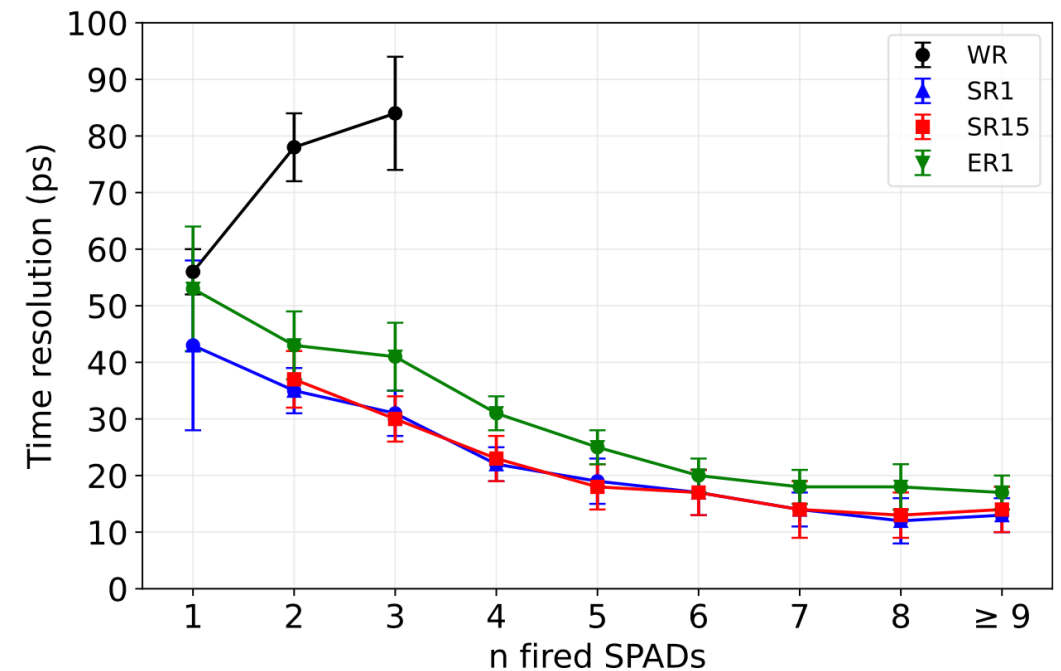
SiPM as charged particle detectors?



recent results exploited Cerenkov light produced in protective resin O(1 mm) of the entrance window making SiPM sensitive to MIP

potential for "compact TOF" (no scintillator!)

potential to make RICH+TOF with SiPM as photosensor



F. Carnesecchi et al., *Eur.Phys.J.Plus* 138 (2023) 9, 788

Note:

previously F. Gramuglia et al, <https://arxiv.org/abs/2111.09998v1> shows results with APD implemented in CMOS tech sensitive to MIP (primary ionization in the silicon)

RICH+TOF?

Note Cerenkov light + TOF is "old" idea:

- Y.Enari NIM A547 (2005) 490 <https://doi.org/10.1016/j.nima.2005.03.159> "TOP" counter
- K.Inami NIM A560 (2006) 303 TOF counter with MCP-PMT
- ALICE T0 detector based on same idea (<http://dx.doi.org/10.1109/NSSMIC.2004.1462267>)

But:

SiPM ("MIP enabled") could be a compact readout choice for a TOF+RICH



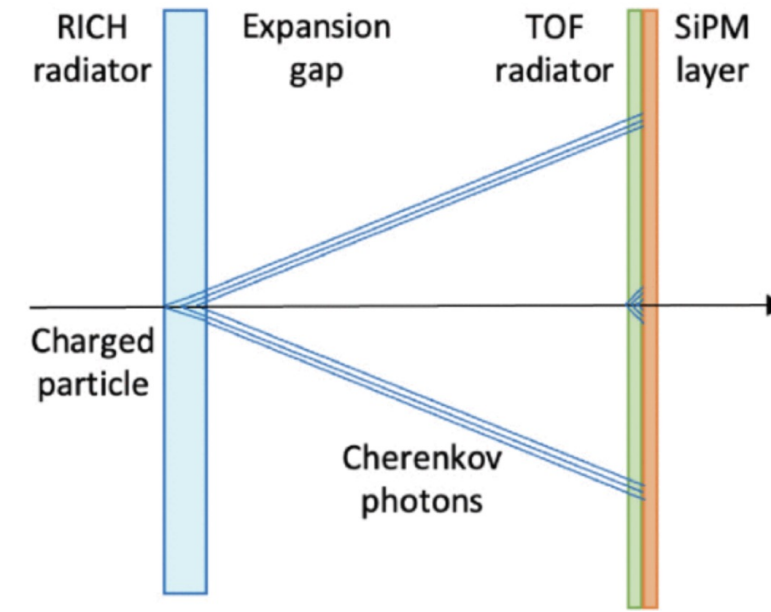
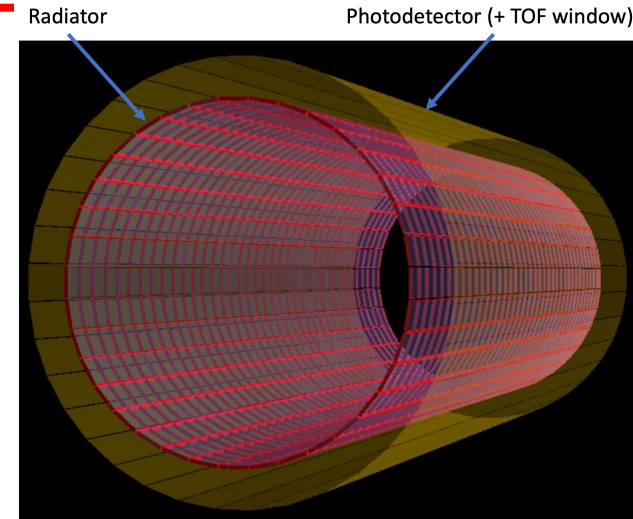
Currently discussed in the context of ALICE 3 Letter of Intent <https://arxiv.org/abs/2211.02491>

"An appealing possibility would be a sensor to detect both MIPs and single photons with high efficiency and good timing capability, such that it can be used both for Cherenkov detection and Time of Flight (TOF) applications."

For TOF applications: 1 mm SiO₂ + 0.45 mm epoxy layer considered on top of Commercial HPK 13360

This design choice would allow one to recover expansion space after radiator (no need of a 2nd TOF layer)

2035 horizon can help to factorize photosensor developments



RICH+TOF?

Note Cerenkov light + TOF is "old" idea:

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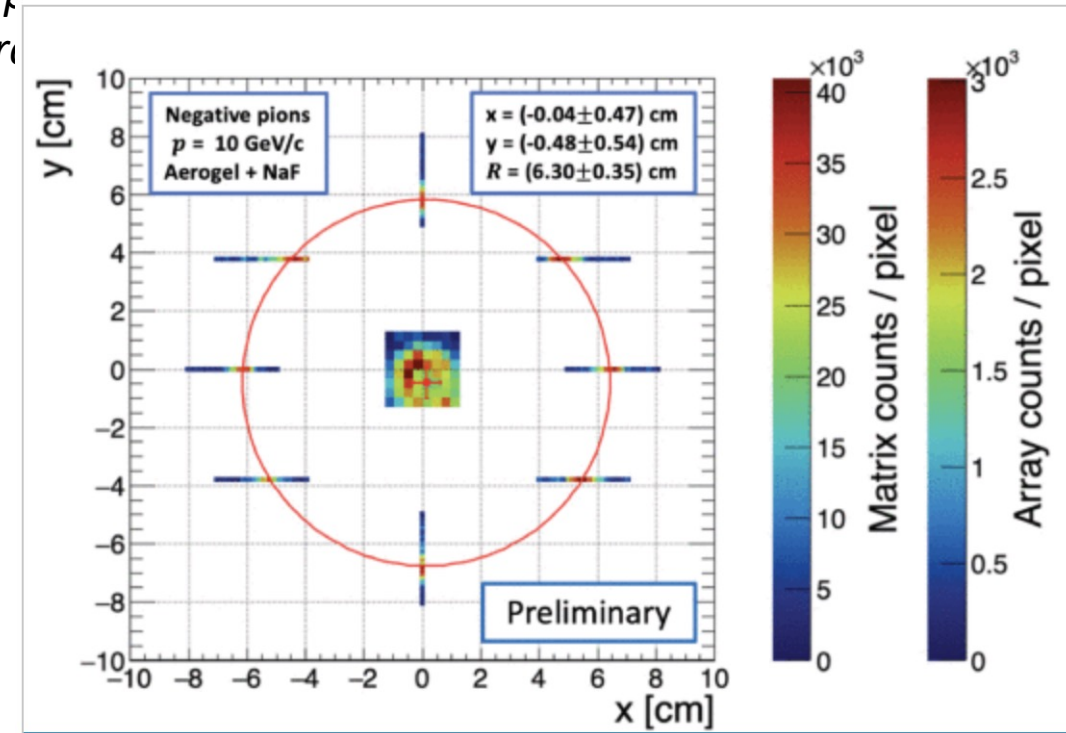
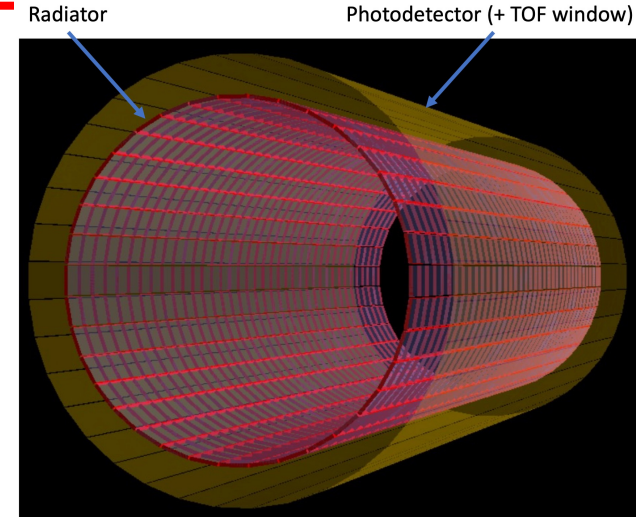
Currently discussed in the context of ALICE 3 Letter of Intent <https://arxiv.org/abs/1802.02491> **Take home message*

"An appealing possibility would be a sensor to detect both MIPs and single photons with high efficiency and good timing capability, such that it can be used both for Cherenkov and Time of Flight (TOF) applications."

Test Beam 2022 (INFN-BA) -->

N. Nicassio et al, doi: [10.1109/IWASI58316.2023.10164558](https://doi.org/10.1109/IWASI58316.2023.10164558)

Equipped with HPK 13361 + NaF window (TOF) and 13352 (RICH)



SiPM R&D highlights relevant for single-photon applications (and potentially better radiation "tolerance")

Digital SiPM

Back side illuminated SiPM (and potential 3D integration)

Light concentration (metamaterial/microlenses)

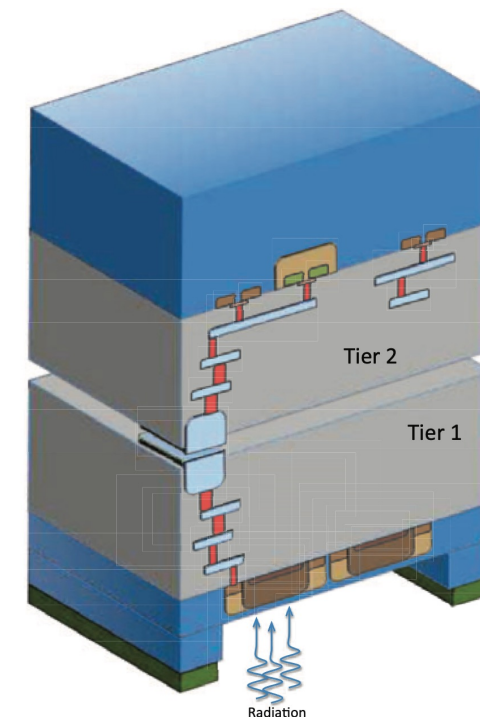
Anti-reflective coating

<https://doi-org.ezproxy.cern.ch/10.1109/NSSMIC.2014.7431246>

E. Charbon et al, A Dual Backside-Illuminated 800-Cell Multi- Channel Digital SiPM with 100 TDCs in 130nm 3D IC Technology

The SiPM was fabricated in a two-tier 130nm CMOS process; the top tier houses 1600 single-photon avalanche diodes (SPADs), organized in a dual 4x200 linear array; the bottom tier houses 2x100 time-to-digital converters (TDCs). Every 8 SPADs there is one shared TDC whose digital output is routed to a 1.04Gps readout interface that enables a total count rate of 80Mcps

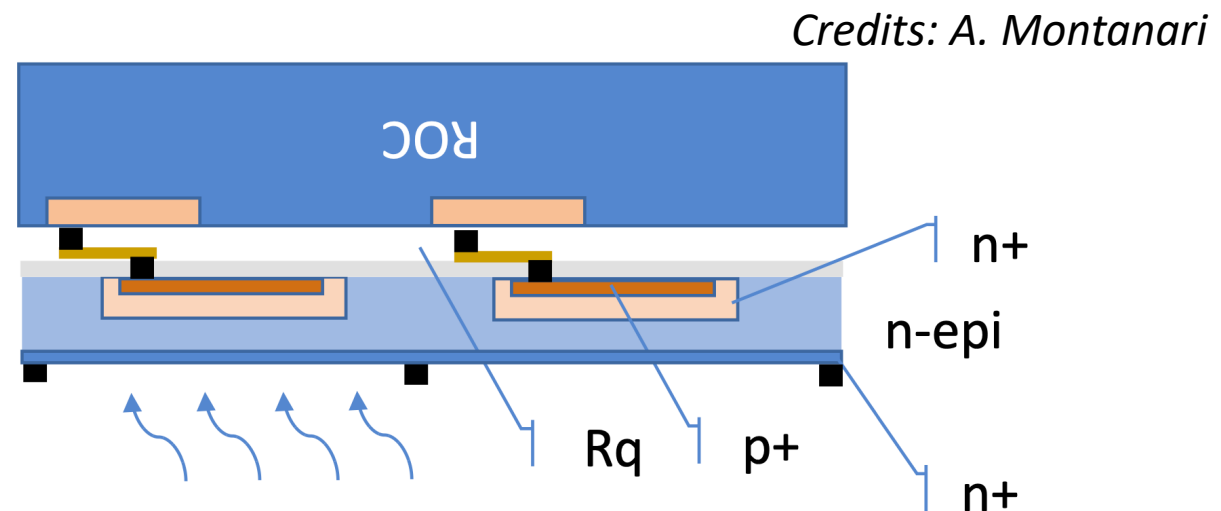
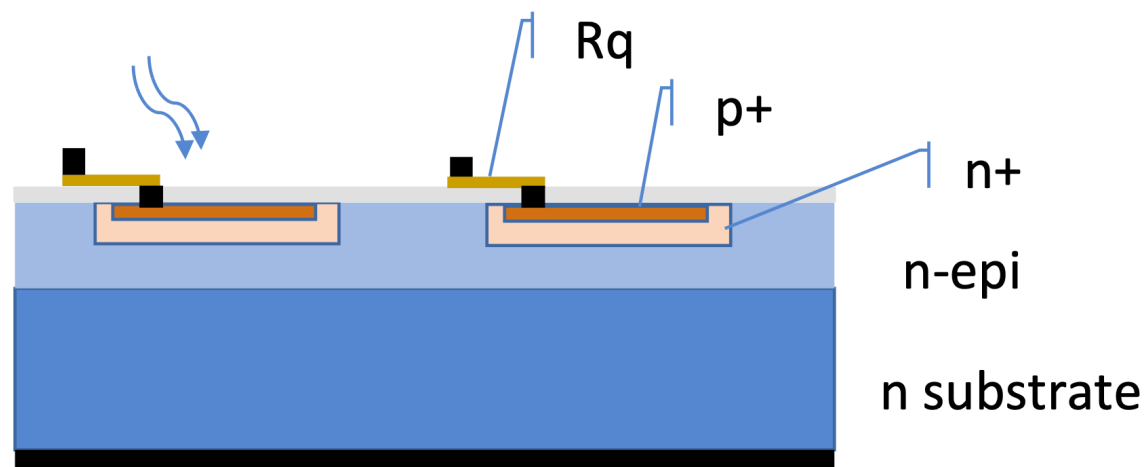
- Very interesting (and challenging) design... no revolution since 2014....
- Digital SiPM triggered wide interest 10 years ago but didn't reach the market
- Philips discontinued Digital SiPM → CMOS process results in a more "noisy" sensor
- Excellent review (from Sherbrooke group): toward "Photon-to-Digital Converter" (PDC) *Sensors* **2021**, 21, 598. <https://doi.org/10.3390/s21020598>



- CMOS technology could make access to commercial technologies but heating from digital circuitry is something to be studied. Unclear if "doable"
- 3D Integration (instead of a pure CMOS) process could be way forward


 *Take home message

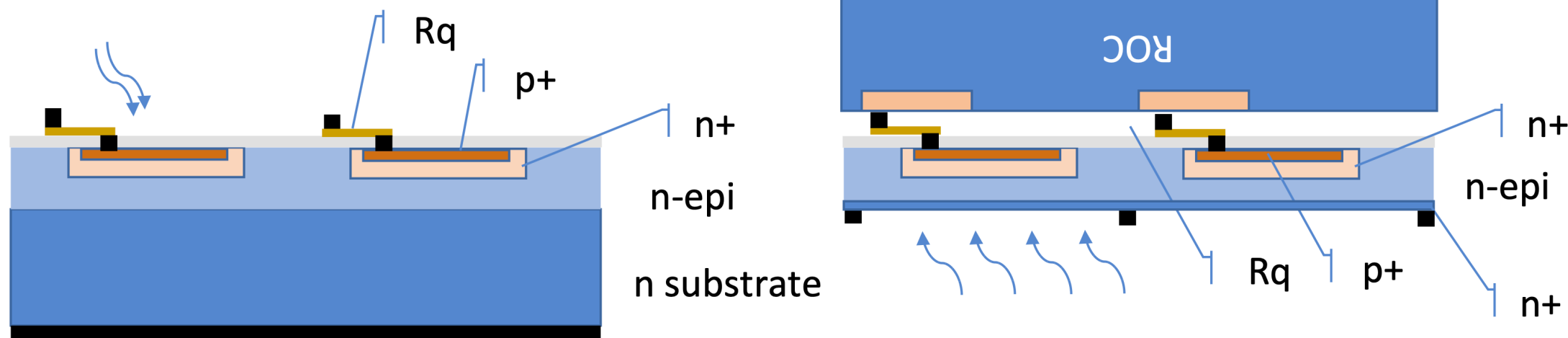
Backside illuminated (BSI) SiPM?



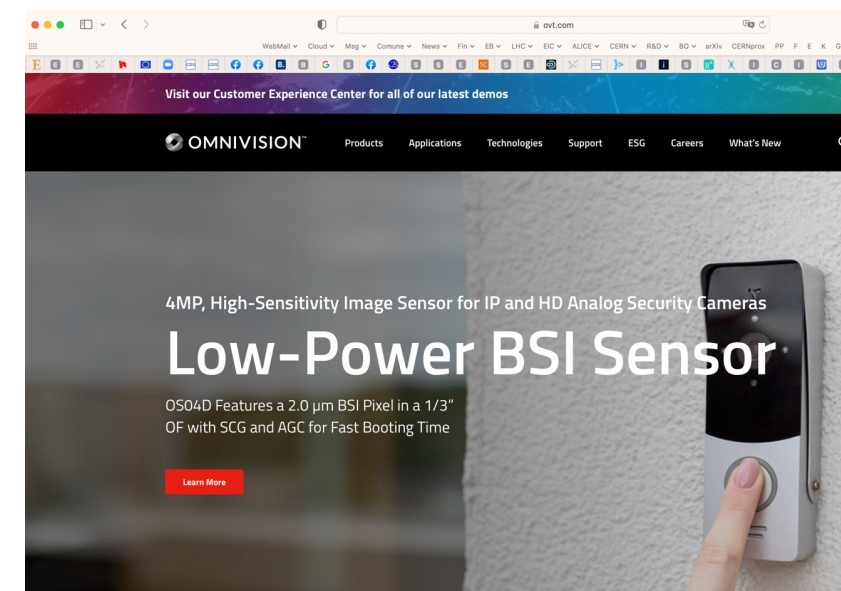
- BSI SiPM would have the obvious advantage of “easy” implementation / routing of readout + increase FF
- Actively researched also in the context of BelleII RICH upgrade (>2030) + AIDAInnova + DUNE + many groups...
- Recent new initiative in CSN3 (IBIS_NEXT)
- First prototype from FBK L. Parrelada-Monreal et al., [Nuclear Inst. and Methods in Physics Research, A 1049 \(2023\) 168042](#)

Backside illuminated (BSI) SiPM?

Credits: A. Montanari



- BSI SiPM would have the obvious advantage of “easy” implementation / routing of readout + increase FF
- Actively researched also in the context of BelleII RICH upgrade (>2030)
- BSI SPAD realized in NIR (900 nm) in the context of LIDAR applications
<https://arxiv.org/abs/2203.01560>
- BSI is now industry standard for consumer and professional imaging sensors (ex. here Omnivision company)
Sensors **2018**, 18(2), 667; <https://doi.org/10.3390/s18020667>



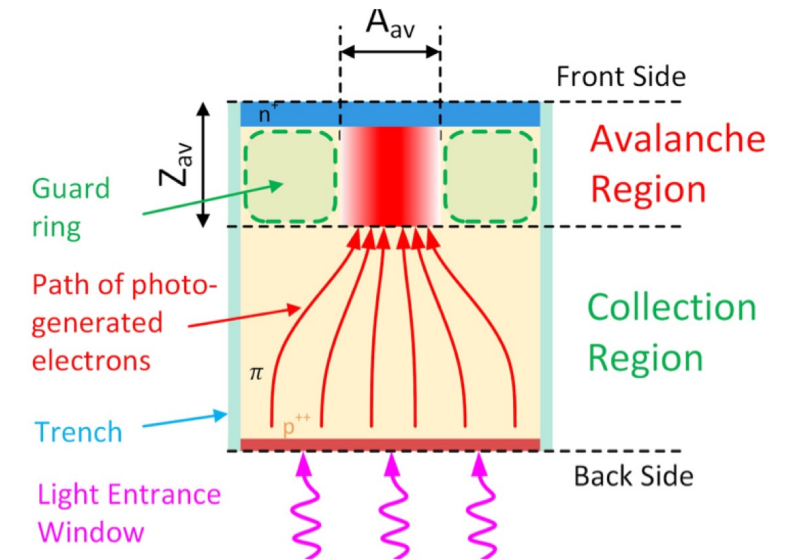
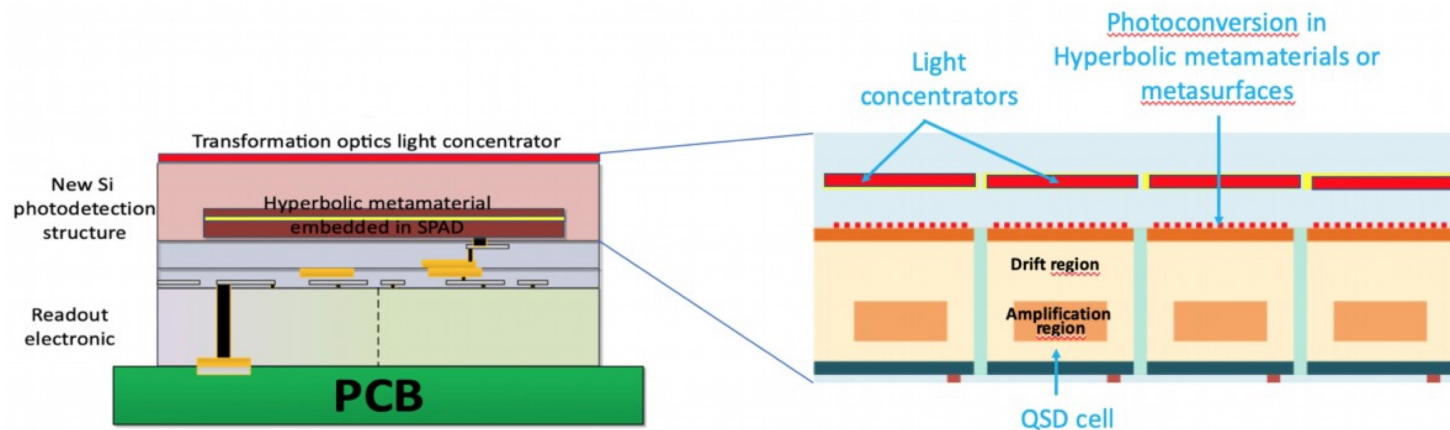
S. Enoch et al., Design considerations for a new generation of SiPMs with unprecedented timing resolution

<https://doi.org/10.48550/arXiv.2101.02952> |

[CERN , INFN-TO, FBK, CNRS (Inst. Fresnel), UPV/Spain]

JINST 16 (2021) 02, P02019

Proposed "Quantum Silicon Detector"



2021 paper that captures together several R&D trends:

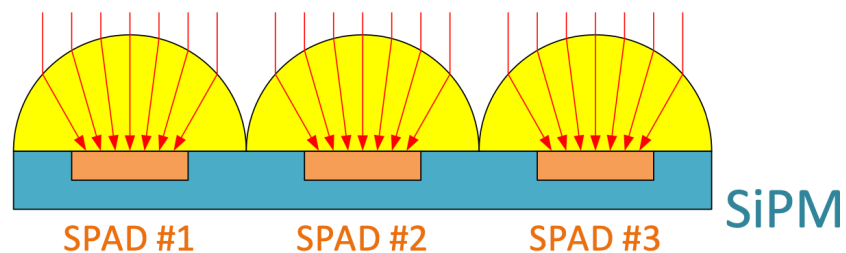
- How to try to implement 3D SiPM getting CMOS tech. elements
- Enhanced optical entrance (light concentrator + metalenses)
- Smaller cell size → less radiation damage
- smaller τ_r → faster recovery time




These R&D might reach a conclusion within this decade (ECFA roadmap)

Microlenses to enhance radiation hardness

- Photons can be focused on a much smaller light-sensitive area within each microcell.
- The silicon *area sensitive to radiation damage is reduced*.



Courtesy from [A. Gola @RICH2022](#)

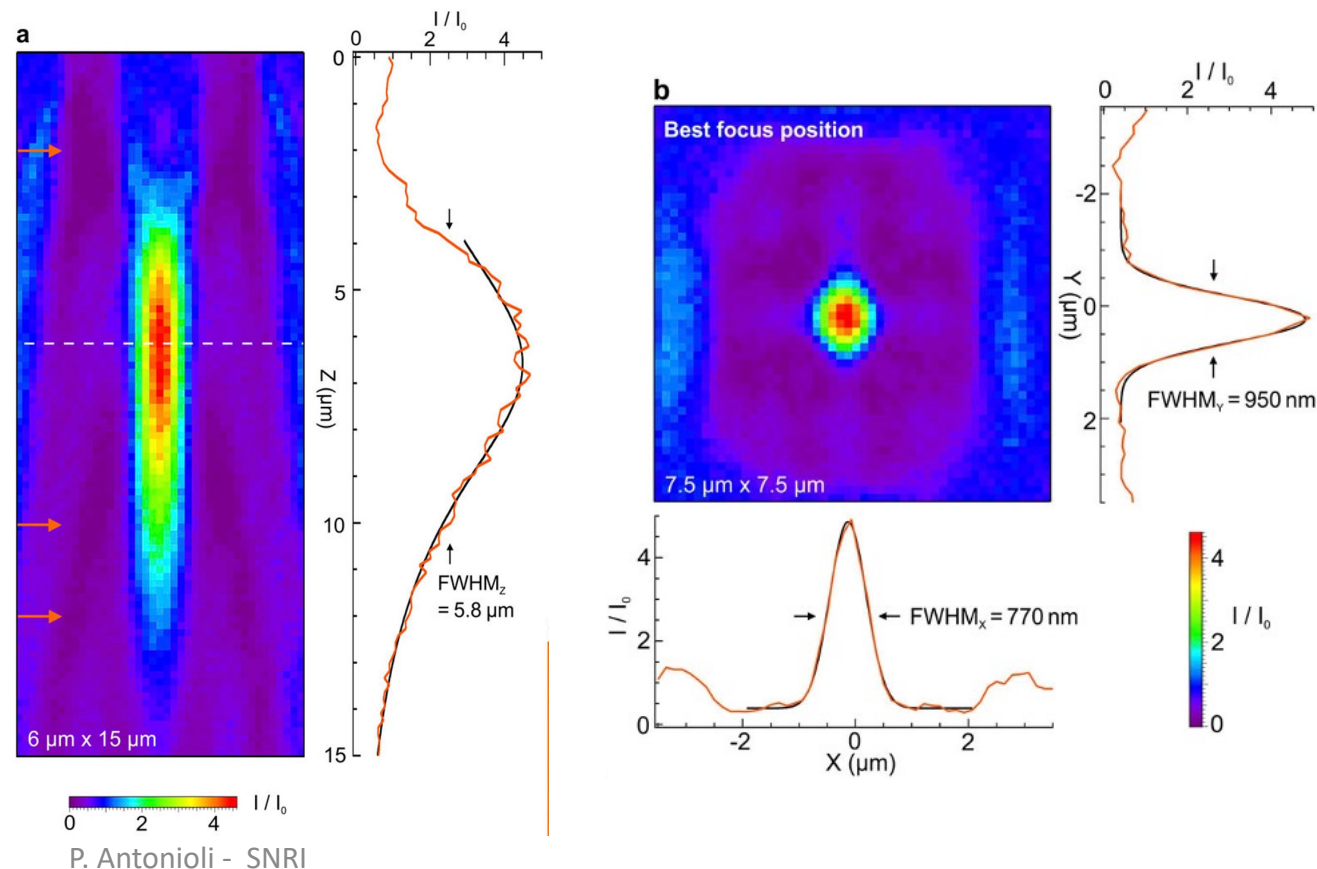
 *Take home message

We can't avoid neutrons to hit silicon in the "sensitive damage regions", but we can curb their area/volume

Microlenses can be used to enhance the Fill Factor (FF) and thus the PDE of the SiPM microcells

Metamaterials for microlensing realized in CMOS compatible process using Nb_2O_5

E. Mikheeva et al, APL Photonics 5 (2020) 116105



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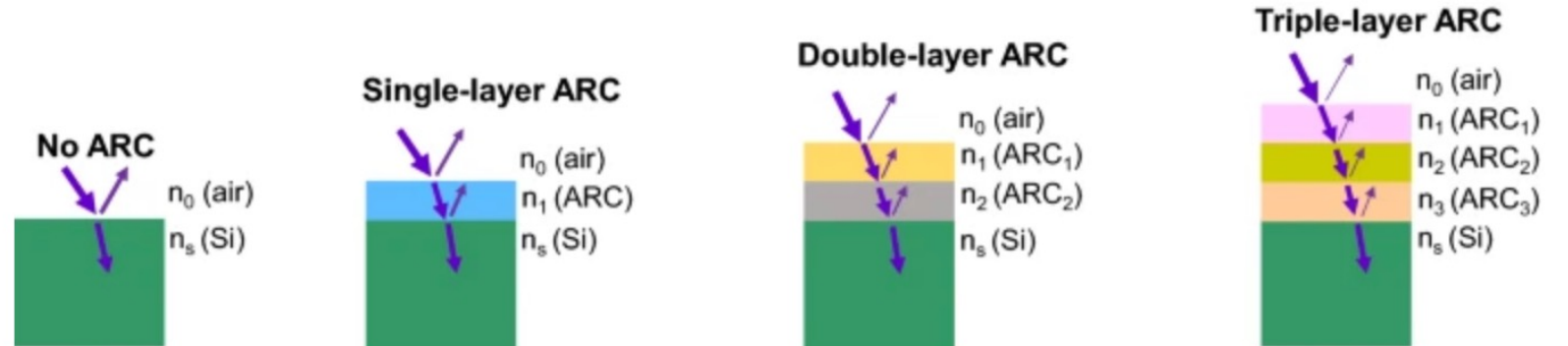
Advanced antireflection for back-illuminated silicon photomultipliers to detect faint light

Yuguo Tao ✉, Arith Rajapakse & Anna Erickson

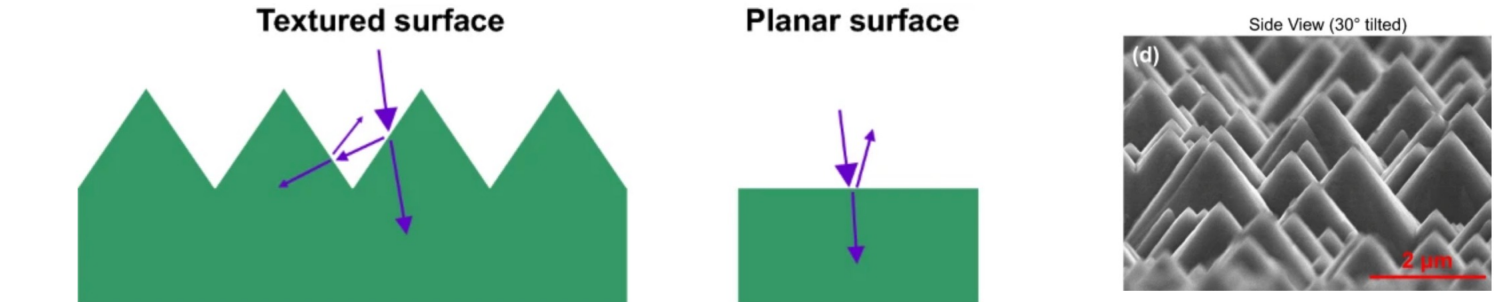
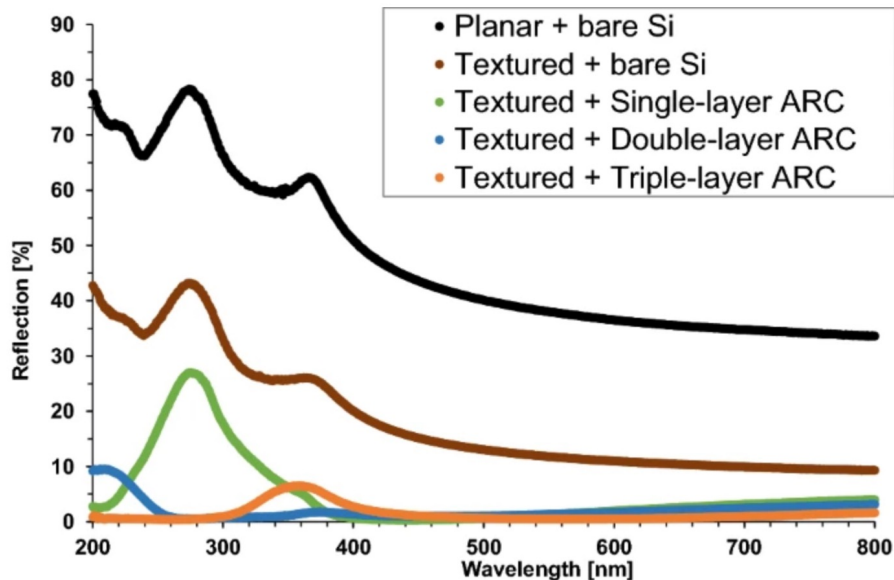
Scientific Reports 12, Article number: 13906 (2022) | Cite this article

<https://doi.org/10.1038/s41598-022-18280-y>

Standard SiPM: ARC materials are thermally grown silicon dioxide (SiO_2) or SiNx /typically one layer



multi-layer ARC on textured surface with upright nano-micro pyramids to reduce the reflection + DARC/TARC



**Take home message*
Combining ARC developments with BSI could be far reaching in FF and PDE for SiPM

We are not alone....

Why Use SiPM Sensors for Automotive LiDAR Applications?




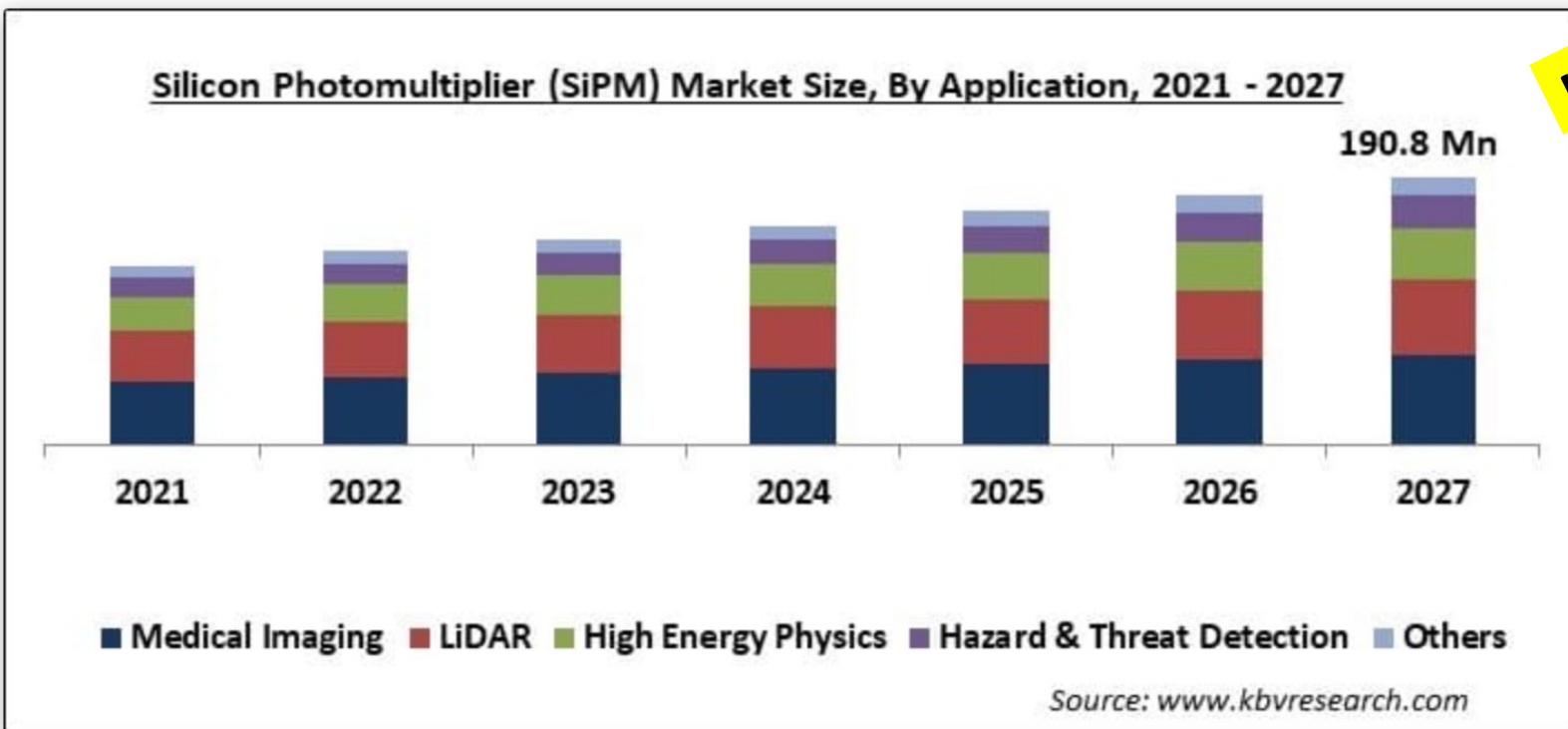
by Deborah Herbert - 03-01-2021

<https://www.onsemi.com/company/news-media/blog/automotive/sipm-sensors-automotive-lidar-applications>

SiPM applications in positron emission tomography: toward ultimate PET time-of-flight resolution

<https://doi.org/10.1140/epjp/s13360-021-01183-8>

P. Lecoq^{1,2,a} , S. Gundacker^{1,3,4}



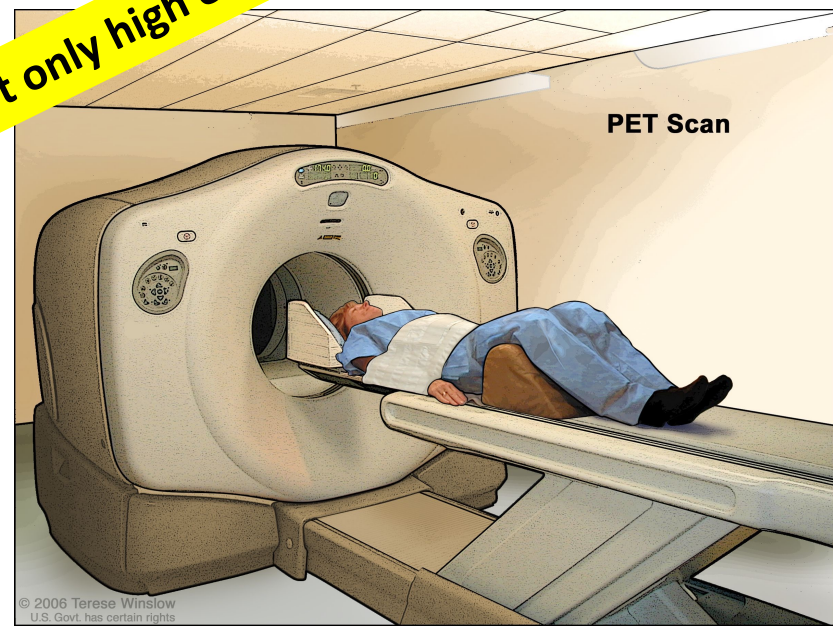
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Il primo sensore SiPM qualificato per uso automotive destinato ad applicazioni LiDAR

Di Massimiliano Luce - 11 Marzo 2021

[f](#) [t](#) [in](#) [p](#) [e](#) [m](#)

Not only high energy physics!





*Take
home message

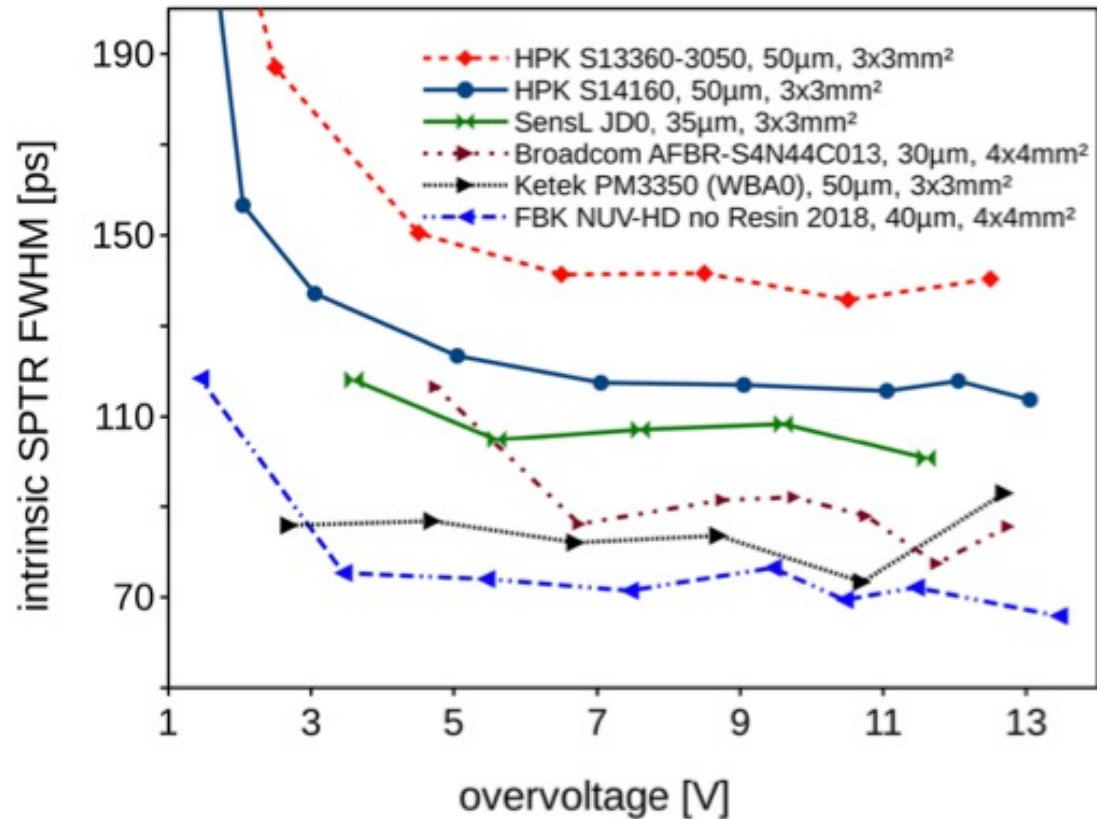
A very dynamic field of research

- SiPM request for NP/HEP will increase: orders by several O(1-10 m²) !
- A need to move away from the “usual (very few) companies”: interesting experience with FBK in Italy. General market trends will help
- SiPM might extend soon its applications to Cerenkov/PID
- For large scale applications cooling and in-situ annealing techniques (at colliders) will be key part of detectors with SiPM-based readout, especially for Cerenkov applications
- There are several technologies developments to be closely watched/followed by our community → combined all together they might enable SiPM “radiation *tolerant* because, despite the damage, they still for purpose” with an unprecedented timing resolution and PDE → potential benefit for innovative detectors is evident

“30 is a great age. You're no longer looked at as a kid and you're not considered old either”

Backup

Intermezzo (II): SiPM and timing resolution

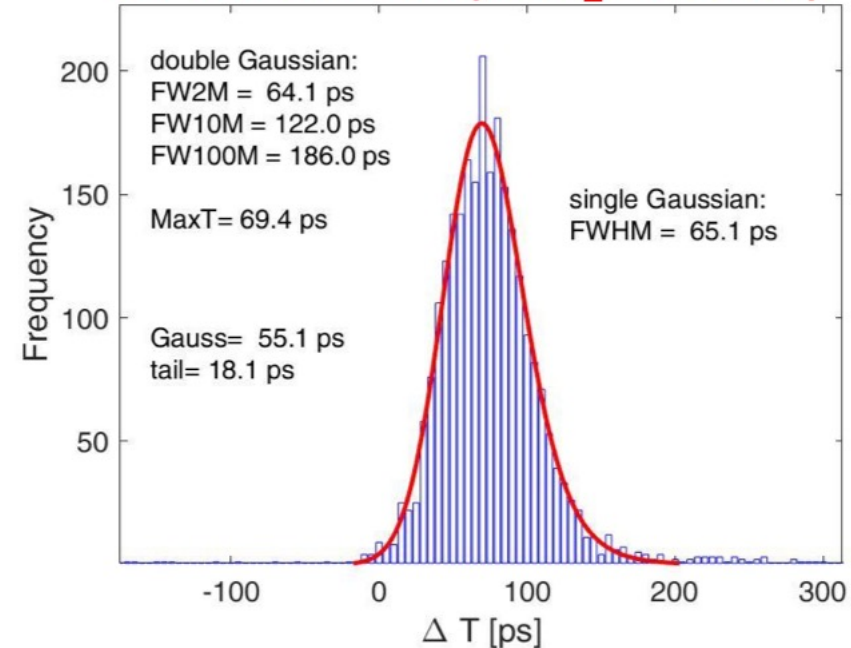


[S. Gundacker et al., Phys. Med. Biol. 65 \(2020\) 025001](#)



many effort in the context of TOF-PET field rapidly evolving also here!

SPTR FWHM (PbF₂ method)



FBK CHK-HD

$$SPTR_{intrinsic} = \sqrt{65^2 - 47^2 - 21^2} = 39.6 \text{ ps}$$

[S. Gundacker at FTM 2022 Worskhop](#)